



OptiMOS™ 和 StrongIRFET™ MOSFETS

选型指南 2019

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OptiMOS™ 和 StrongIRFET™

20-300 V MOSFET N-沟道功率MOSFET

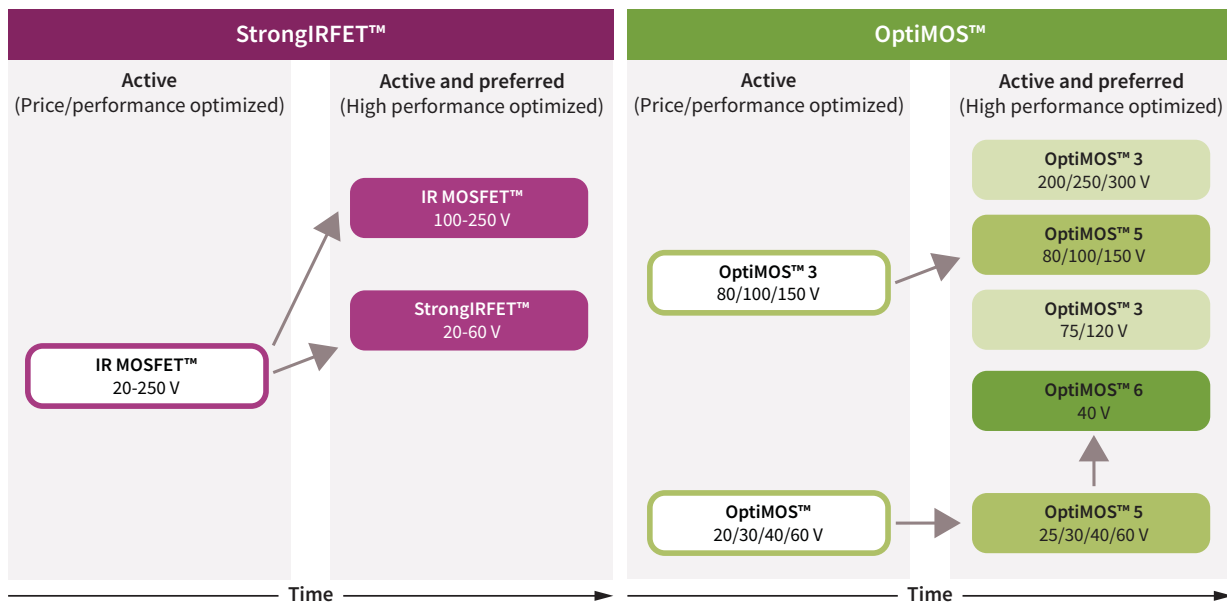
英飞凌半导体的设计初衷是实现更高的效率、功率密度和成本效益。全系列 OptiMOS™ 和 StrongIRFET™ 功率 MOSFET 实现了许多应用领域的创新和性能提升, 如开关式电源 (SMPS)、电池供电应用、电机控制和驱动、逆变器、计算机 (电源)。

英飞凌高度创新的 OptiMOS™ 和 StrongIRFET™ 系列始终满足电源系统设计中关键规格的最高质量和性能需要, 如导通电阻 ($R_{DS(on)}$) 和 优值(FOM)。

OptiMOS™ 功率MOSFET性能一流, 产品特征包括超低 $R_{DS(on)}$, 以及高开关频率应用的低充电负荷。StrongIRFET™ 功率MOSFET专为驱动应用而设计, 对于低开关频率的设计以及需要高载流能力的设计非常理想。

StrongIRFET™	OptiMOS™
超高性价比	一流的技术
专为工业应用而设计	专为高性能应用而设计
针对低开关频率而优化	针对高开关频率而优化
高载流能力	行业最佳品质因数
粗糙硅	高效率 and 功率密度
	

技术开发和产品系列定位

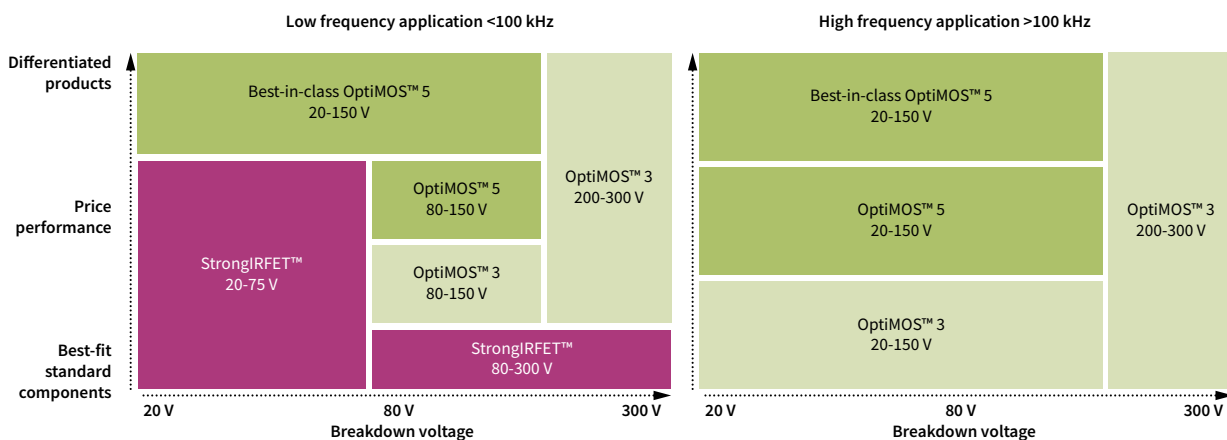


英飞凌功率MOSFET 20-300 V 产品组合分为“积极首选组合”，即指能够实现一流性能的最新技术，以及“积极组合”，由能够实现广泛产品组合的成熟技术组成。

OptiMOS™ 6 功率MOSFET 40 V 是OptiMOS™ 产品系列的新成员，可使用 SuperSO8 或 PQFN 3.3 x 3.3 封装。当需要产出一流 (BiC) 的产品并实现各种输出功率的高效率时，该技术是完美解决方案。对于其他电压等级，从 25 V 到 150 V，OptiMOS™ 5 代表市场上的最新一代产品，提供一流 (BiC) 解决方案或价格/性能解决方案。对于高频应用，OptiMOS™ 3 功率MOSFET 40-50 V 作为标准部件补充了产品组合。积极和首选的 OptiMOS™ 3 功率MOSFET 75-120 V 和 200-300 V 是低频或高频应用的最佳匹配组合，涉及各种产品，从 BiC 到标准零件。

当 BiC 性能属于非必要因素，而成本是更重要的因素时，建议 20-300 V 应用采用 StrongIRFET™ Gen. 1。

以下图表按照开关频率总结最佳匹配标准部件、价格/性能和不同产品的推荐技术。



应用和电压等级指南

OptiMOS™ 和 StrongIRFET™ 组合, 包括 20 至 300 V MOSFET, 可满足各种需要, 从低开关频率到高开关频率。下表是针对每个主要子应用和电压等级而推荐的 OptiMOS™ 或 StrongIRFET™ 产品的指南概要。

推荐电压		20-30 V	40 V	60 V	75-80 V	100 V	135-150 V	200 V	250 V	300 V	
电池供电	低功率 电动工具、多旋翼 飞机、电池、工业驱 动装置	OptiMOS™	✓	✓	✓	✓					
		StrongIRFET™	✓	✓	✓	✓					
	大功率 (LEV, LSEV)	OptiMOS™			✓	✓	✓	✓	✓		
		StrongIRFET™			✓	✓	✓	✓	✓		
换流器	太阳能	OptiMOS™			✓	✓	✓	✓			
		StrongIRFET™			✓	✓	✓				
	不间断电源	慢速切换									
		OptiMOS™	✓	✓	✓	✓	✓	✓	✓	✓	✓
		StrongIRFET™	✓	✓	✓	✓	✓	✓	✓	✓	✓
		快速切换									
	OptiMOS™	✓	✓	✓	✓	✓	✓	✓	✓	✓	
	StrongIRFET™	✓	✓	✓	✓	✓	✓	✓	✓	✓	
脱机	OptiMOS™		✓	✓							
	StrongIRFET™		✓	✓							
SMPS	适配器/ 充电器	OptiMOS™		✓	✓	✓	✓				
		StrongIRFET™		✓	✓	✓	✓				
	计算机电源	OptiMOS™		✓	✓						
		StrongIRFET™		✓	✓						
	液晶电视	OptiMOS™			✓	✓	✓				
		StrongIRFET™			✓	✓	✓				
	服务器	OptiMOS™		✓	✓	✓					
		StrongIRFET™		✓	✓	✓					
	AC-DC	OptiMOS™				✓	✓	✓	✓		
		StrongIRFET™				✓	✓				
	电信	OptiMOS™	✓	✓	✓	✓	✓	✓			
		StrongIRFET™	✓	✓	✓	✓	✓				






推荐 StrongIRFET™






推荐 OptiMOS™

可使用 StrongIRFET™

可使用 OptiMOS™

小体积高性能封装

	TO-247	TO-220	D ² PAK	D ² PAK 7-针	TO-无铅
					
	针对高功率应用和高电流能力而优化				
高度 [mm]	5.0	4.4	4.4	4.4	2.3
外形 [mm]	40.15 x 15.9	29.5 x 10.0	15.0 x 10.0	15.0 x 10.0	11.68 x 9.9
电流能力 [A]	195.0	195.0	195.0	240.0	300.0
热阻 R_{thJC} [K/W]	2.0	0.5	0.5	0.5	0.4

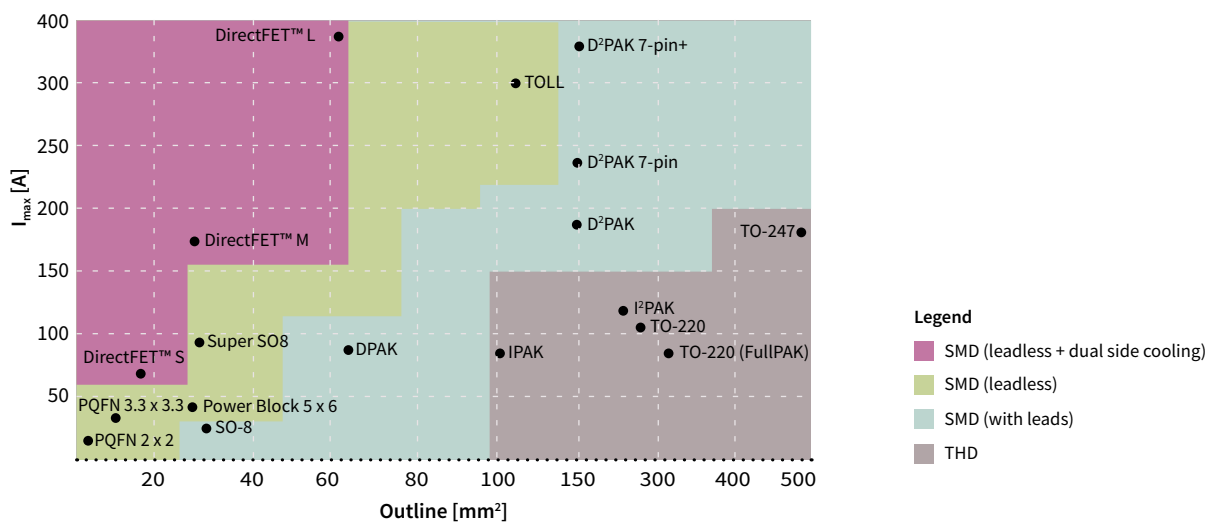
	SuperSO8	电源模块	PQFN 3.3 x 3.3	PQFN 2 x 2	DirectFET™
					
	可实现最高效率和功率管理	设计体积显著减小	可实现最高效率和功率管理	大大节省空间	占用空间小, 热性能最佳
高度 [mm]	1.0	1.0	1.0	0.9	小型: 0.65 中型: 0.65 大型: 0.71
外形 [mm]	5.15 x 6.15	5.0 x 6.0	3.3 x 3.3	2.0 x 2.0	小型: 4.8 x 3.8 中型: 6.3 x 4.9 大型: 9.1 x 6.98
电流能力 [A]	100.0	50.0	40.0	18.5	小型: 75.0 中型: 180.0 大型: 375.0
热阻 R_{thJC} [K/W]	0.8	1.5	3.2	11.1	0.5

独立和集成封装

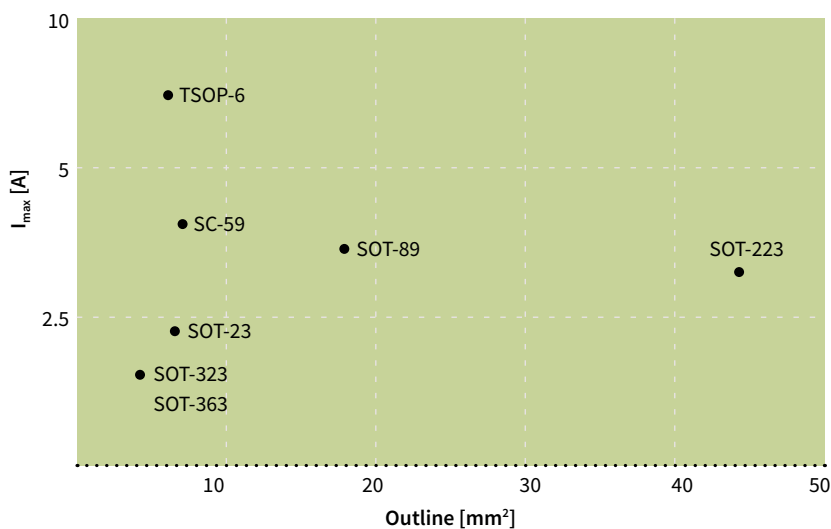
不同封装形式的 OptiMOS™ 和 StrongIRFET™ 技术均可提供, 从而满足更高载流能力和大大节省空间的需求。

广泛的产品组合可减小占用空间、增大电流额定值、优化热性能。表面贴装无铅装置可减小占用空间, 而通孔封装拥有额定功率高的特征。

而且, 英飞凌提供如 DirectFET™ and TO-无铅的创新型封装。DirectFET™ 寄生电阻较低, 专为高频率应用而设计。该封装具有三种不同的尺寸: 小型、中型和大型。TO-无铅经优化后可处理最大 300 A 的电流, 增加了功率密度, 大大减少了占用空间。



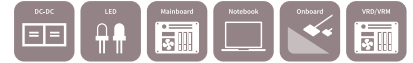
小信号和小功率MOSFET。



小信号和小功率MOSFET拥有八种工业标准封装类型, 从最大的 SOT-223 到最小的 SOT-363。

产品有单配置、双配置、互补配置, 用途广泛, 包括电池保护、LED 照明、低压驱动装置和直流-直流变换器。

OptiMOS™ 和 StrongIRFET™ 20 V (超级) 逻辑电平



$R_{DS(on)}$ max @ $V_{GS}=10$ V [mΩ]	TO-252 (DPAK)	DirectFET™	PQFN 2 x 2	PQFN 3.3 x 3.3	SuperSO8	SO-8	SOT-23
< 1		IRL6283MTRPBF $R_{DS(on)}=0.65$ mΩ			IRFH6200TRPBF $R_{DS(on)}=0.99$ mΩ		
2-4	IRLR6225TRPBF $R_{DS(on)}=4.0$ mΩ	IRL6297SDTRPBF** $R_{DS(on)}=3.8$ mΩ; 双			BSC026N02KS G $R_{DS(on)}=2.6$ mΩ IRLH6224TRPBF $R_{DS(on)}=3.0$ mΩ	IRF6201TRPBF $R_{DS(on)}=2.45$ mΩ	
4-10					BSC046N02KS G $R_{DS(on)}=4.6$ mΩ	IRF3717 $R_{DS(on)}=4.4$ mΩ	
> 10			IRLHS6242TRPBF $R_{DS(on)}=11.7$ mΩ				IRLML6244 ¹⁾ *** $R_{DS(on)}=21$ mΩ
			IRLHS6276TRPBF** $R_{DS(on)}=45.0$ mΩ; 双				IRLML6246 ¹⁾ *** $R_{DS(on)}=46$ mΩ

OptiMOS™ 和 StrongIRFET™ 25 V 逻辑电平



$R_{DS(on)}$ max @ $V_{GS}=10$ V [mΩ]	DirectFET™	PQFN 2 x 2	PQFN 3.3 x 3.3	SuperSO8	SO-8	SOT-23
< 1	IRF6718L2TRPBF $R_{DS(on)}=0.7$ mΩ			BSC009NE2LS $R_{DS(on)}=0.9$ mΩ		
	BSB008NE2LX $R_{DS(on)}=0.8$ mΩ		BSZ009NE2LS ²⁾ $R_{DS(on)}=0.9$ mΩ	BSC009NE2LS5 $R_{DS(on)}=0.9$ mΩ		
				BSC009NE2LS51** $R_{DS(on)}=0.95$ mΩ		
1-2	IRF6898MTRPBF** $R_{DS(on)}=1.1$ mΩ		BSZ010NE2LS ²⁾ $R_{DS(on)}=1.0$ mΩ	BSC010NE2LS $R_{DS(on)}=1.0$ mΩ		
	BSB012NE2LXI** $R_{DS(on)}=1.2$ mΩ		BSZ011NE2LS ²⁾ $R_{DS(on)}=1.1$ mΩ	BSC010NE2LS1** $R_{DS(on)}=1.05$ mΩ		
	IRF6717MTRPBF $R_{DS(on)}=1.25$ mΩ		BSZ013NE2LS51** $R_{DS(on)}=1.3$ mΩ	BSC014NE2LS1** $R_{DS(on)}=1.4$ mΩ		
	IRF6894MTRPBF** $R_{DS(on)}=1.3$ mΩ		BSZ014NE2LS5IF *** $R_{DS(on)}=1.45$ mΩ	IRFH5250D $R_{DS(on)}=1.4$ mΩ		
	BSB013NE2LXI** $R_{DS(on)}=1.3$ mΩ		BSZ017NE2LS51** $R_{DS(on)}=1.7$ mΩ	BSC015NE2LS51** $R_{DS(on)}=1.5$ mΩ		
	IRF6797MTRPBF** $R_{DS(on)}=1.4$ mΩ		BSZ018NE2LS $R_{DS(on)}=1.8$ mΩ	BSC018NE2LS $R_{DS(on)}=1.8$ mΩ		
	IRF6716M $R_{DS(on)}=1.6$ mΩ		BSZ018NE2LS1** $R_{DS(on)}=1.8$ mΩ	BSC018NE2LS1** $R_{DS(on)}=1.8$ mΩ		
	IRF6715MTRPBF $R_{DS(on)}=1.6$ mΩ					
	IRF6893MTRPBF** $R_{DS(on)}=1.6$ mΩ					
	IRF6892STRPBF** $R_{DS(on)}=1.7$ mΩ					
IRF6795MTRPBF** $R_{DS(on)}=1.8$ mΩ						
2-4	IRF6714MTRPBF $R_{DS(on)}=2.1$ mΩ		BSZ031NE2LS5 $R_{DS(on)}=3.1$ mΩ	BSC024NE2LS $R_{DS(on)}=2.4$ mΩ		
	BSF030NE2LQ $R_{DS(on)}=3.0$ mΩ		BSZ033NE2LS5 $R_{DS(on)}=3.3$ mΩ	BSC026NE2LS5 $R_{DS(on)}=2.6$ mΩ	IRF8252 $R_{DS(on)}=2.7$ mΩ	
	BSF035NE2LQ $R_{DS(on)}=3.5$ mΩ		BSZ036NE2LS $R_{DS(on)}=3.6$ mΩ	BSC032NE2LS $R_{DS(on)}=3.2$ mΩ		
	IRF6811STRPBF** $R_{DS(on)}=3.7$ mΩ		BSZ037NE2LS ²⁾ $R_{DS(on)}=3.7$ mΩ			
			BSZ039NE2LS ²⁾ $R_{DS(on)}=3.9$ mΩ			
4-10	IRF6802SD $R_{DS(on)}=4.2$ mΩ					
	IRF6710S2TRPBF $R_{DS(on)}=4.5$ mΩ		IRFHM8228TRPBF $R_{DS(on)}=5.2$ mΩ	BSC050NE2LS $R_{DS(on)}=5.0$ mΩ		
	IRF6712STRPBF $R_{DS(on)}=4.9$ mΩ		BSZ060NE2LS $R_{DS(on)}=6.0$ mΩ			
	IRF6810STRPBF** $R_{DS(on)}=5.2$ mΩ		IRFHM8235TRPBF $R_{DS(on)}=7.7$ mΩ			
> 10		IRFHS8242 $R_{DS(on)}=13$ mΩ				IRFML8244 $R_{DS(on)}=24$ mΩ

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* 针对谐振应用优化(如, LLC 变流器)

** 单片集成肖特基二极管

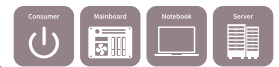
*** $R_{DS(on)}$ max @ $V_{GS}=4.5$ V

¹⁾ 2.5 V_{GS} 驱动能力

²⁾ 即将发布

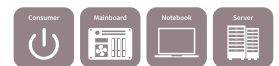


OptiMOS™ 和 StrongIRFET™ 25 V/30 V, 功率级 3 x 3 和 5 x 6



零件编号	封装	单片集成类肖特基二极管	BV _{DSS} [V]	R _{DS(on), max.} [mΩ] @ V _{GS} =4.5 V max.		Q _g [nC] @ V _{GS} =4.5 V 类型	
				高压侧	低压侧	高压侧	低压侧
BSZ0910ND	TISON 3 x 3	-	30	13	13	4.0	4.0
BSZ0909ND	TISON 3 x 3	-	30	25	25	1.8	1.8
BSC0910NDI	TISON 5 x 6	✓	25	5.9	1.6	7.7	25.0
BSC0911ND	TISON 5 x 6	-	25	4.8	1.7	7.7	25.0
BSC0921NDI	TISON 5 x 6	✓	30	7.0	2.1	5.8	21.0
BSC0923NDI	TISON 5 x 6	✓	30	7.0	3.7	5.2	12.2
BSC0924NDI	TISON 5 x 6	✓	30	7.0	5.2	5.2	8.6
BSC0925ND	TISON 5 x 6	-	30	6.4	6.4	5.2	6.7

OptiMOS™ 和 StrongIRFET™ 25 V/30 V, 电源模块 5 x 6 和 5 x 4



零件编号	封装	单片集成类肖特基二极管	BV _{DSS} [V]	R _{DS(on), max.} [mΩ] @ V _{GS} =4.5 V max.		Q _g [nC] @ V _{GS} =4.5 V 类型	
				高压侧	低压侧	高压侧	低压侧
BSG0810NDI	TISON 5 x 6	✓	25	4.0	1.2	5.6	16.0
BSG0811ND	TISON 5 x 6	-	25	4.0	1.1	5.6	20.0
BSG0813NDI	TISON 5 x 6	✓	25	4.0	1.7	5.6	12.0
IRFH4257DTRPBF	PQFN 5 x 4	✓	25	4.7	1.8	9.7	23.0

OptiMOS™ 和 StrongIRFET™ 30 V 逻辑电平



$R_{DS(on)}$ max. @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-针)	TO-220
< 1			IPB009N03L G $R_{DS(on)}=0.95\text{ m}\Omega$	
1-2		IRLS3813TRLPBF $R_{DS(on)}=1.95\text{ m}\Omega$		IRLB3813PBF $R_{DS(on)}=1.95\text{ m}\Omega$
2-4	IRLR8743TRPBF $R_{DS(on)}=3.1\text{ m}\Omega$			IRLB8314PBF $R_{DS(on)}=2.4\text{ m}\Omega$
	IPD031N03L G $R_{DS(on)}=3.1\text{ m}\Omega$			IRL3713PBF $R_{DS(on)}=3.0\text{ m}\Omega$
		IPB034N03L G $R_{DS(on)}=3.4\text{ m}\Omega$		IRLB8743PBF $R_{DS(on)}=3.2\text{ m}\Omega$
4-10	IPD040N03L G $R_{DS(on)}=4.0\text{ m}\Omega$			IPP034N03L G $R_{DS(on)}=3.4\text{ m}\Omega$
	IPD050N03L G $R_{DS(on)}=5.0\text{ m}\Omega$	IPB042N03L G $R_{DS(on)}=4.2\text{ m}\Omega$		IPP042N03L G $R_{DS(on)}=4.2\text{ m}\Omega$
	IRLR8726TRPBF $R_{DS(on)}=5.8\text{ m}\Omega$	IPB055N03L G $R_{DS(on)}=5.5\text{ m}\Omega$		IRLB8748PBF $R_{DS(on)}=4.8\text{ m}\Omega$
	IPD060N03L G $R_{DS(on)}=6.0\text{ m}\Omega$	IPB065N03L G $R_{DS(on)}=6.5\text{ m}\Omega$		IPP055N03L G $R_{DS(on)}=5.5\text{ m}\Omega$
	IPD075N03L G $R_{DS(on)}=7.5\text{ m}\Omega$	IPB080N03L G $R_{DS(on)}=8.0\text{ m}\Omega$		IRL8113PBF $R_{DS(on)}=6.0\text{ m}\Omega$
	IRLR8729TRPBF $R_{DS(on)}=8.9\text{ m}\Omega$			IRLB8721PBF $R_{DS(on)}=8.7\text{ m}\Omega$
	IPD090N03L G $R_{DS(on)}=9.0\text{ m}\Omega$			
	IPD135N03L G $R_{DS(on)}=13.5\text{ m}\Omega$			
10-25	IRLR3103 $R_{DS(on)}=19.0\text{ m}\Omega$			

OptiMOS™ 和 StrongIRFET™ 30 V 逻辑电平



$R_{DS(on)}$ max. @ $V_{GS}=10\text{ V}$ [mΩ]	裸芯片 ($R_{DS(on)}$ 典型)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	TO-无铅
< 1					IPT004N03L $R_{DS(on)}=0.4\text{ m}\Omega$
1-2				IRFH8303TRPBF $R_{DS(on)}=1.1\text{ m}\Omega$	
				BSC011N03LS $R_{DS(on)}=1.1\text{ m}\Omega$	
				BSC011N03LSI** $R_{DS(on)}=1.1\text{ m}\Omega$	
				BSC011N03LST $R_{DS(on)}=1.1\text{ m}\Omega$	
				IRFH8307TRPBF $R_{DS(on)}=1.3\text{ m}\Omega$	
		IRF8301MTRPBF $R_{DS(on)}=1.5\text{ m}\Omega$		BSC0500NSI** $R_{DS(on)}=1.3\text{ m}\Omega$	
			BSZ0500NSI** $R_{DS(on)}=1.5\text{ m}\Omega$	BSC014N03LS G $R_{DS(on)}=1.4\text{ m}\Omega$	
		IRF8302MTRPBF** $R_{DS(on)}=1.8\text{ m}\Omega$	BSZ019N03LS $R_{DS(on)}=1.9\text{ m}\Omega$	BSC0901NS $R_{DS(on)}=1.9\text{ m}\Omega$	
		BSZ0901NS $R_{DS(on)}=2.0\text{ m}\Omega$	BSC0501NSI** $R_{DS(on)}=1.9\text{ m}\Omega$		
	IPC055N03L3*** $R_{DS(on)}=2.7\text{ m}\Omega$		BSZ0501NSI** $R_{DS(on)}=2.0\text{ m}\Omega$	BSC0901NSI** $R_{DS(on)}=2.0\text{ m}\Omega$	

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** 单片集成肖特基二极管

*** $R_{DS(on)}$ 典型 @ $V_{GS}=4.5\text{ V}$

OptiMOS™ 和 StrongIRFET™ 30 V 逻辑电平



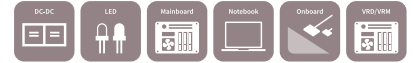
$R_{DS(on), max.}$ @ $V_{GS}=10V$ [mΩ]	裸芯片 ($R_{DS(on)}$ 典型)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	SO-8	SO-8 双	PQFN 2 x 2
2-4		IRF8304MTRPBF $R_{DS(on)}=2.2\text{ m}\Omega$	BSZ0901NSI** $R_{DS(on)}=2.1\text{ m}\Omega$	BSC020N03LS G $R_{DS(on)}=2.0\text{ m}\Omega$			
	IPC042N03L3**** $R_{DS(on)}=3.7\text{ m}\Omega$		IRLHM620TRPBF $R_{DS(on)}=2.5\text{ m}\Omega$	BSC0502NSI** $R_{DS(on)}=2.4\text{ m}\Omega$			
		IRF8306MTRPBF** $R_{DS(on)}=2.5\text{ m}\Omega$	BSZ0902NS $R_{DS(on)}=2.6\text{ m}\Omega$	BSC025N03LS G $R_{DS(on)}=2.5\text{ m}\Omega$			
				BSC0902NS $R_{DS(on)}=2.6\text{ m}\Omega$			
				IRF8252TRPBF $R_{DS(on)}=2.7\text{ m}\Omega$			
			BSZ0902NSI** $R_{DS(on)}=2.8\text{ m}\Omega$	BSC0902NSI** $R_{DS(on)}=2.8\text{ m}\Omega$	IRF8788TRPBF $R_{DS(on)}=2.8\text{ m}\Omega$		
			BSZ0502NSI** $R_{DS(on)}=2.8\text{ m}\Omega$	IRFH8316TRPBF $R_{DS(on)}=2.95\text{ m}\Omega$			
				BSC030N03LS G $R_{DS(on)}=3.0\text{ m}\Omega$			
			BSZ0503NSI** $R_{DS(on)}=3.4\text{ m}\Omega$	IRFH8318TRPBF $R_{DS(on)}=3.1\text{ m}\Omega$			
			IRLHM630**** $R_{DS(on)}=3.5\text{ m}\Omega$	BSC0503NSI** $R_{DS(on)}=3.2\text{ m}\Omega$	IRF7862TRPBF $R_{DS(on)}=3.3\text{ m}\Omega$		
			BSZ035N03LS G $R_{DS(on)}=3.5\text{ m}\Omega$	BSC034N03LS G $R_{DS(on)}=3.4\text{ m}\Omega$	IRF8734TRPBF $R_{DS(on)}=3.5\text{ m}\Omega$		
	4-10			IRFHM830 $R_{DS(on)}=3.8\text{ m}\Omega$	BSC0504NSI** $R_{DS(on)}=3.7\text{ m}\Omega$		
			BSZ0904NSI** $R_{DS(on)}=4.0\text{ m}\Omega$	BSC0904NSI** $R_{DS(on)}=3.7\text{ m}\Omega$			
			IRFHM830D $R_{DS(on)}=4.3\text{ m}\Omega$	IRFH8324TRPBF $R_{DS(on)}=4.1\text{ m}\Omega$			
			BSZ0506NS $R_{DS(on)}=4.4\text{ m}\Omega$	BSC042N03LS G $R_{DS(on)}=4.2\text{ m}\Omega$			
			IRFHM8326TRPBF $R_{DS(on)}=4.7\text{ m}\Omega$	BSC0906NS $R_{DS(on)}=4.5\text{ m}\Omega$			
				IRFH8321TRPBF $R_{DS(on)}=4.9\text{ m}\Omega$			
IPC028N03L3 $R_{DS(on)}=5.0\text{ m}\Omega$			BSZ050N03LS G $R_{DS(on)}=5.0\text{ m}\Omega$	IRFH8325TRPBF $R_{DS(on)}=5.0\text{ m}\Omega$	IRF8736TRPBF $R_{DS(on)}=4.8\text{ m}\Omega$		
			BSZ058N03LS G $R_{DS(on)}=5.8\text{ m}\Omega$	BSC050N03LS G $R_{DS(on)}=5.0\text{ m}\Omega$			
IPC022N03L3 $R_{DS(on)}=5.3\text{ m}\Omega$			IRFH8329TRPBF $R_{DS(on)}=6.1\text{ m}\Omega$	BSC052N03LS $R_{DS(on)}=5.2\text{ m}\Omega$			
			BSZ065N03LS $R_{DS(on)}=6.5\text{ m}\Omega$	BSC057N03LS G $R_{DS(on)}=5.7\text{ m}\Omega$			
		IRF8327S2 $R_{DS(on)}=7.3\text{ m}\Omega$	IRFH8330TRPBF $R_{DS(on)}=6.6\text{ m}\Omega$	IRFH8330TRPBF $R_{DS(on)}=6.6\text{ m}\Omega$			
			BSZ0994NS $R_{DS(on)}=7.0\text{ m}\Omega$	BSC080N03LS G $R_{DS(on)}=8.0\text{ m}\Omega$			
10-63	IPC014N03L3 $R_{DS(on)}=10.3\text{ m}\Omega$		IRFHM831 $R_{DS(on)}=7.8\text{ m}\Omega$	IRFH8334TRPBF $R_{DS(on)}=9.0\text{ m}\Omega$	IRF8721TRPBF $R_{DS(on)}=8.5\text{ m}\Omega$		
			BSZ088N03LS G $R_{DS(on)}=8.8\text{ m}\Omega$	BSC090N03LS G $R_{DS(on)}=9.0\text{ m}\Omega$	IRF8714TRPBF $R_{DS(on)}=8.7\text{ m}\Omega$		
			IRFH8334TRPBF $R_{DS(on)}=9.0\text{ m}\Omega$	BSC0909NS $R_{DS(on)}=9.2\text{ m}\Omega$			
			BSZ100N03LS G $R_{DS(on)}=10.0\text{ m}\Omega$				
			BSZ0909NS $R_{DS(on)}=12.0\text{ m}\Omega$	BSC120N03LS G $R_{DS(on)}=12.0\text{ m}\Omega$	IRF8707TRPBF $R_{DS(on)}=11.9\text{ m}\Omega$	IRF7907TRPBF $R_{DS(on)}=11.8\text{ m}\Omega+16.4\text{ m}\Omega$	IRLHS6342*** $R_{DS(on)}=16\text{ m}\Omega$
			IRFH8337TRPBF $R_{DS(on)}=12.4\text{ m}\Omega$	IRFH8337TRPBF $R_{DS(on)}=12.8\text{ m}\Omega$	IRL6342 ¹⁾ *** $R_{DS(on)}=14.6\text{ m}\Omega$	IRF8513TRPBF $R_{DS(on)}=2.7\text{ m}\Omega+15.5\text{ m}\Omega$	IRFHS8342 $R_{DS(on)}=16\text{ m}\Omega$
2 x 7.2					IRL6372 ¹⁾ *** $R_{DS(on)}=18\text{ m}\Omega$; 双	IRF8313TRPBF $R_{DS(on)}=15.5\text{ m}\Omega+15.5\text{ m}\Omega$	IRLHS6376*** $R_{DS(on)}=63\text{ m}\Omega$; 双
						IRF7905TRPBF $R_{DS(on)}=17.1\text{ m}\Omega+21.8\text{ m}\Omega$	
2 x 15				BSC072N03LD G $R_{DS(on)}=7.2\text{ m}\Omega$			
				BSC150N03LD G $R_{DS(on)}=15.0\text{ m}\Omega$			

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¹⁾ 2.5 V_{GS} 驱动能力
** 单片集成肖特基二极管

*** $R_{DS(on), max}$ @ $V_{GS}=4.5\text{ V}$
**** $R_{DS(on), 典型}$ @ $V_{GS}=4.5\text{ V}$

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$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	PQFN 3.3 x 3.3	SuperSO8	SO-8	SO-8 双	SOT-23	TSOP-6
1-2		BSC014N03MS G $R_{DS(on)}=1.4\text{ m}\Omega$				
		BSC016N03MS G $R_{DS(on)}=1.6\text{ m}\Omega$				
		BSC020N03MS G $R_{DS(on)}=2.0\text{ m}\Omega$				
2-4		BSC025N03MS G $R_{DS(on)}=2.5\text{ m}\Omega$	BSO033N03MS G $R_{DS(on)}=3.3\text{ m}\Omega$			
	BSZ035N03MS G $R_{DS(on)}=3.5\text{ m}\Omega$	BSC030N03MS G $R_{DS(on)}=3.0\text{ m}\Omega$	BSO040N03MS G $R_{DS(on)}=4.0\text{ m}\Omega$			
4-10		BSC042N03MS G $R_{DS(on)}=4.2\text{ m}\Omega$				
	BSZ050N03MS G $R_{DS(on)}=5.0\text{ m}\Omega$	BSC050N03MS G $R_{DS(on)}=5.0\text{ m}\Omega$				
		BSC057N03MS G $R_{DS(on)}=5.7\text{ m}\Omega$				
	BSZ058N03MS G $R_{DS(on)}=5.8\text{ m}\Omega$	BSC080N03MS G $R_{DS(on)}=8.0\text{ m}\Omega$				
	BSZ088N03MS G $R_{DS(on)}=8.8\text{ m}\Omega$	BSC090N03MS G $R_{DS(on)}=9.0\text{ m}\Omega$				
	BSZ100N03MS G $R_{DS(on)}=10.0\text{ m}\Omega$	BSC100N03MS G $R_{DS(on)}=10.0\text{ m}\Omega$				
>10	BSZ130N03MS G $R_{DS(on)}=13.0\text{ m}\Omega$	BSC120N03MS G $R_{DS(on)}=12.0\text{ m}\Omega$	BSO110N03MS G $R_{DS(on)}=11.0\text{ m}\Omega$		IRLML0030 $R_{DS(on)}=27\text{ m}\Omega$	IRLTS6342*** $R_{DS(on)}=14.6\text{ m}\Omega$
					IRLML6344 ¹⁾ *** $R_{DS(on)}=29\text{ m}\Omega$	IRF7S8342 $R_{DS(on)}=19\text{ m}\Omega$
					IRLML6346 ¹⁾ *** $R_{DS(on)}=63\text{ m}\Omega$	
					IRLML2030 $R_{DS(on)}=100\text{ m}\Omega$	
2 x 15				BSO150N03MD G $R_{DS(on)}=15.0\text{ m}\Omega$		
2 x 22				BSO220N03MD G $R_{DS(on)}=22.0\text{ m}\Omega$		



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$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-针)	TO-220	TO-247	裸芯片 ($R_{DS(on)}$ 典型)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	TO-220 FullPAK
< 1			IRFS7430TRL7PP $R_{DS(on)}=0.75\text{ m}\Omega$			IPC218N04N3 $R_{DS(on)}=0.9\text{ m}\Omega$				
1-2		IRFS7430TRLPBF $R_{DS(on)}=1.3\text{ m}\Omega$	IRFS7434TRL7PP $R_{DS(on)}=1.0\text{ m}\Omega$	IRFB7430PBF $R_{DS(on)}=1.3\text{ m}\Omega$	IRFP7430PBF $R_{DS(on)}=1.3\text{ m}\Omega$	IPC171N04N $R_{DS(on)}=1.1\text{ m}\Omega$	IRF7739L1TRPBF $R_{DS(on)}=1.0\text{ m}\Omega$		IRFH7084TRPBF $R_{DS(on)}=1.25\text{ m}\Omega$	
		IPB015N04N G $R_{DS(on)}=1.5\text{ m}\Omega$	IPB011N04N G $R_{DS(on)}=1.1\text{ m}\Omega$	IPPO15N04N G $R_{DS(on)}=1.5\text{ m}\Omega$			IRF7480MTRPBF $R_{DS(on)}=1.2\text{ m}\Omega$		IRFH7004TRPBF $R_{DS(on)}=1.4\text{ m}\Omega$	
		IRFS3004 $R_{DS(on)}=1.75\text{ m}\Omega$	IRFS3004-7P $R_{DS(on)}=1.25\text{ m}\Omega$				IRF7946TRPBF $R_{DS(on)}=1.4\text{ m}\Omega$		BSC017N04NS G $R_{DS(on)}=1.7\text{ m}\Omega$	
		IRFS7434TRLPBF $R_{DS(on)}=1.6\text{ m}\Omega$	IRFS7437TRL7PP $R_{DS(on)}=1.4\text{ m}\Omega$	IRFB7434PBF $R_{DS(on)}=1.6\text{ m}\Omega$			BSB015N04NX3 G $R_{DS(on)}=1.5\text{ m}\Omega$		IRF40H210 $R_{DS(on)}=1.7\text{ m}\Omega$	
		IRFS7437TRLPBF $R_{DS(on)}=1.8\text{ m}\Omega$	IPB020N04N G $R_{DS(on)}=2.0\text{ m}\Omega$	IRFB7437PBF $R_{DS(on)}=2.0\text{ m}\Omega$			IRF40DM229 $R_{DS(on)}=1.85\text{ m}\Omega$		BSC019N04NS G $R_{DS(on)}=1.9\text{ m}\Omega$	
2-4	IRFR7440TRPBF $R_{DS(on)}=2.4\text{ m}\Omega$			IPPO23N04N G $R_{DS(on)}=2.3\text{ m}\Omega$			IRF7483MTRPBF $R_{DS(on)}=2.3\text{ m}\Omega$		IRFH7440TRPBF $R_{DS(on)}=2.4\text{ m}\Omega$	
	IRFR7446TRPBF $R_{DS(on)}=3.9\text{ m}\Omega$	IRFS7440TRLPBF $R_{DS(on)}=2.5\text{ m}\Omega$		IRFB7440PBF $R_{DS(on)}=2.5\text{ m}\Omega$					BSC030N04NS G $R_{DS(on)}=3.0\text{ m}\Omega$	
		IRF1404S $R_{DS(on)}=4.0\text{ m}\Omega$		IRFB7446PBF $R_{DS(on)}=3.3\text{ m}\Omega$					IRFH7446TRPBF $R_{DS(on)}=3.3\text{ m}\Omega$	
4-10				IPPO41N04N G $R_{DS(on)}=4.1\text{ m}\Omega$					BSC054N04NS G $R_{DS(on)}=5.4\text{ m}\Omega$	IPA041N04N G $R_{DS(on)}=4.1\text{ m}\Omega$
	IRF40R207 $R_{DS(on)}=5.1\text{ m}\Omega$			IRF40B207 $R_{DS(on)}=4.5\text{ m}\Omega$						
				IPPO48N04N G $R_{DS(on)}=4.8\text{ m}\Omega$						
>10								BSZ105N04NS G $R_{DS(on)}=10.5\text{ m}\Omega$		
								BSZ165N04NS G $R_{DS(on)}=16.5\text{ m}\Omega$		

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¹⁾ 2.5 V_{GS} 驱动能力
*** $R_{DS(on)}$ max @ $V_{GS}=4.5\text{ V}$



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$R_{DS(on), max.}$ @ $V_{GS}=10V$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-针)	TO-220	TO-247	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	TO-无铅
< 1			IRL40SC228 $R_{DS(on)}=0.65\text{ m}\Omega$			IRL7472L1TRPBF $R_{DS(on)}=0.45\text{ m}\Omega$		BSC007N04LS6 $R_{DS(on)}=0.7\text{ m}\Omega$	IRL40T209 $R_{DS(on)}=0.8\text{ m}\Omega$
			IRL40SC209 $R_{DS(on)}=0.8\text{ m}\Omega$						
1-2		IPB015N04L G $R_{DS(on)}=1.5\text{ m}\Omega$	IPB011N04L G $R_{DS(on)}=1.1\text{ m}\Omega$	IRL40B209 $R_{DS(on)}=1.25\text{ m}\Omega$	IRLP3034PBF $R_{DS(on)}=1.7\text{ m}\Omega$	BSB014N04LX3 G $R_{DS(on)}=1.4\text{ m}\Omega$		BSC010N04LS $R_{DS(on)}=1.0\text{ m}\Omega$	
		IRLS3034TRLPBF $R_{DS(on)}=1.7\text{ m}\Omega$	IRLS3034TRL7P $R_{DS(on)}=1.4\text{ m}\Omega$	IRLB3034PBF $R_{DS(on)}=1.7\text{ m}\Omega$		IRL7486MTRPBF $R_{DS(on)}=1.4\text{ m}\Omega$		BSC010N04LS6 $R_{DS(on)}=1.0\text{ m}\Omega$	
		IRL40S212 $R_{DS(on)}=1.9\text{ m}\Omega$		IRL40B212 $R_{DS(on)}=1.9\text{ m}\Omega$				BSC010N04LST $R_{DS(on)}=1.0\text{ m}\Omega$	
								BSC010N04LSI $R_{DS(on)}=1.05\text{ m}\Omega$	
								BSC010N04LSC * $R_{DS(on)}=1.05\text{ m}\Omega$	
								BSC014N04LST $R_{DS(on)}=1.4\text{ m}\Omega$	
								BSC014N04LS $R_{DS(on)}=1.4\text{ m}\Omega$	
								BSC014N04LSI $R_{DS(on)}=1.45\text{ m}\Omega$	
2-4				IRL40B215 $R_{DS(on)}=2.7\text{ m}\Omega$				BSC016N04LS G $R_{DS(on)}=1.6\text{ m}\Omega$	
							BSZ018N04LS6 $R_{DS(on)}=1.8\text{ m}\Omega$	BSC018N04LS G $R_{DS(on)}=1.8\text{ m}\Omega$	
								BSC019N04LS $R_{DS(on)}=1.9\text{ m}\Omega$	
								BSC019N04LST $R_{DS(on)}=1.9\text{ m}\Omega$	
					IPP039N04L G $R_{DS(on)}=3.9\text{ m}\Omega$			BSC022N04LS $R_{DS(on)}=2.2\text{ m}\Omega$	
								BSC022N04LS6 $R_{DS(on)}=2.2\text{ m}\Omega$	
4-10							BSZ024N04LS6 $R_{DS(on)}=2.4\text{ m}\Omega$	BSC026N04LS $R_{DS(on)}=2.6\text{ m}\Omega$	
							BSZ025N04LS $R_{DS(on)}=2.5\text{ m}\Omega$	BSC027N04LS G $R_{DS(on)}=2.7\text{ m}\Omega$	
							BSZ028N04LS $R_{DS(on)}=2.8\text{ m}\Omega$	BSC032N04LS $R_{DS(on)}=3.2\text{ m}\Omega$	
	IPD036N04L G $R_{DS(on)}=3.6\text{ m}\Omega$	IRL1404S $R_{DS(on)}=4.0\text{ m}\Omega$					BSZ034N04LS $R_{DS(on)}=3.4\text{ m}\Omega$	BSC035N04LS G $R_{DS(on)}=3.5\text{ m}\Omega$	
	IRLR31142TRPBF $R_{DS(on)}=4.5\text{ m}\Omega$						BSZ040N04LS G $R_{DS(on)}=4.0\text{ m}\Omega$	BSC050N04LS G $R_{DS(on)}=5.0\text{ m}\Omega$	
							BSZ063N04LS6 $R_{DS(on)}=6.3\text{ m}\Omega$	BSC059N04LS G $R_{DS(on)}=5.9\text{ m}\Omega$	
								BSC059N04LS6 $R_{DS(on)}=5.9\text{ m}\Omega$	
							BSZ097N04LS G $R_{DS(on)}=9.7\text{ m}\Omega$	BSC093N04LS G $R_{DS(on)}=9.3\text{ m}\Omega$	

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3) 即将发布
* 爬电距离增加



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$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ⁺ PAK)	TO-263 (D ⁺ PAK 7-针)	TO-262 (I ⁺ PAK)	TO-220	TO-220 FullPAK	TO-247
1-2			IPB010N06N ²⁾ $R_{DS(on)}=1.0\text{ m}\Omega$				
			IRFS7530TRL7PP $R_{DS(on)}=1.4\text{ m}\Omega$				
			IPB014N06N ²⁾ $R_{DS(on)}=1.4\text{ m}\Omega$				
			IPB017N06N3 G $R_{DS(on)}=1.7\text{ m}\Omega$				
2-4		IRFS7530TRLPBF $R_{DS(on)}=2.0\text{ m}\Omega$	IRFS7534TRL7PP $R_{DS(on)}=1.95\text{ m}\Omega$	IPI020N06N ²⁾ $R_{DS(on)}=2.0\text{ m}\Omega$	IRFB7530PBF $R_{DS(on)}=2.0\text{ m}\Omega$		IRFP7530PBF $R_{DS(on)}=2.0\text{ m}\Omega$
	IPD025N06N ²⁾ $R_{DS(on)}=2.5\text{ m}\Omega$	IRFS7534TRLPBF $R_{DS(on)}=2.4\text{ m}\Omega$	IRFS3006TRL7PP $R_{DS(on)}=2.1\text{ m}\Omega$		IPP020N06N ²⁾ $R_{DS(on)}=2.0\text{ m}\Omega$		
		IRFS3006 $R_{DS(on)}=2.5\text{ m}\Omega$		IPI024N06N3 G $R_{DS(on)}=2.4\text{ m}\Omega$	IRFB7534PBF $R_{DS(on)}=2.4\text{ m}\Omega$		
		IPB026N06N ²⁾ $R_{DS(on)}=2.6\text{ m}\Omega$			IPP024N06N3 G ²⁾ $R_{DS(on)}=2.4\text{ m}\Omega$		IRFP3006PBF $R_{DS(on)}=2.5\text{ m}\Omega$
		IPB029N06N3 G $R_{DS(on)}=2.9\text{ m}\Omega$		IPI029N06N ²⁾ $R_{DS(on)}=2.9\text{ m}\Omega$	IPP029N06N ²⁾ $R_{DS(on)}=2.9\text{ m}\Omega$	IPA029N06N ²⁾ $R_{DS(on)}=2.9\text{ m}\Omega$	IRFP3206PBF $R_{DS(on)}=3.0\text{ m}\Omega$
	IPD033N06N ²⁾ $R_{DS(on)}=3.3\text{ m}\Omega$	IRFS3206 $R_{DS(on)}=3.0\text{ m}\Omega$		IPI032N06N3 G $R_{DS(on)}=3.2\text{ m}\Omega$	IPP032N06N3 G $R_{DS(on)}=3.2\text{ m}\Omega$	IPA032N06N3 G $R_{DS(on)}=3.2\text{ m}\Omega$	
	IPD034N06N3 G $R_{DS(on)}=3.4\text{ m}\Omega$	IRFS7537TRLPBF $R_{DS(on)}=3.3\text{ m}\Omega$			IRFB7537PBF $R_{DS(on)}=3.3\text{ m}\Omega$		IRFP7537PBF $R_{DS(on)}=3.3\text{ m}\Omega$
	IPD038N06N3 G $R_{DS(on)}=3.8\text{ m}\Omega$	IPB037N06N3 G $R_{DS(on)}=3.7\text{ m}\Omega$			IPP040N06N3 G $R_{DS(on)}=4.0\text{ m}\Omega$		
		IRFS3306 $R_{DS(on)}=4.2\text{ m}\Omega$		IPI040N06N3 G $R_{DS(on)}=4.0\text{ m}\Omega$	IPP040N06N ²⁾ $R_{DS(on)}=4.0\text{ m}\Omega$	IPA040N06N ²⁾ $R_{DS(on)}=4.0\text{ m}\Omega$	
	4-10	IRFR7540TRPBF $R_{DS(on)}=4.8\text{ m}\Omega$	IRFS7540TRLPBF $R_{DS(on)}=5.1\text{ m}\Omega$			IRFB7540PBF $R_{DS(on)}=5.1\text{ m}\Omega$	IPA057N06N3 G $R_{DS(on)}=5.7\text{ m}\Omega$
IPD053N06N ²⁾ $R_{DS(on)}=5.3\text{ m}\Omega$		IPB054N06N3 G $R_{DS(on)}=5.4\text{ m}\Omega$			IPP057N06N3 G ²⁾ $R_{DS(on)}=5.7\text{ m}\Omega$		
		IPB057N06N ²⁾ $R_{DS(on)}=5.7\text{ m}\Omega$			IRFB7545PBF $R_{DS(on)}=5.9\text{ m}\Omega$		
IRFR7546TRPBF $R_{DS(on)}=7.9\text{ m}\Omega$		IRF1018ES $R_{DS(on)}=8.4\text{ m}\Omega$			IPP060N06N ²⁾ $R_{DS(on)}=6.0\text{ m}\Omega$	IPA060N06N ²⁾ $R_{DS(on)}=6.0\text{ m}\Omega$	
IPD088N06N3 G $R_{DS(on)}=8.8\text{ m}\Omega$					IRF60B217 $R_{DS(on)}=9.0\text{ m}\Omega$	IPA093N06N3 G $R_{DS(on)}=9.3\text{ m}\Omega$	
IRF60R217 $R_{DS(on)}=9.9\text{ m}\Omega$		IPB090N06N3 G $R_{DS(on)}=9.0\text{ m}\Omega$			IPP093N06N3 G $R_{DS(on)}=9.3\text{ m}\Omega$		
>10		IRFS3806 $R_{DS(on)}=15.8\text{ m}\Omega$					



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$R_{DS(on), max.}$ @ $V_{GS}=10V$ [mΩ]	裸芯片 ($R_{DS(on)}$ 典型)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	TO-无铅
< 1					IPT007N06N ²⁾ $R_{DS(on)}=0.7 m\Omega$
1-2	IPC218N06N3 $R_{DS(on)}=1.3 m\Omega$	IRF7749L1TRPBF $R_{DS(on)}=1.5 m\Omega$		BSC012N06NS $R_{DS(on)}=1.2 m\Omega$	IPT012N06N ²⁾ $R_{DS(on)}=1.2 m\Omega$
				BSC014N06NS ²⁾ $R_{DS(on)}=1.4 m\Omega$	
				BSC014N06NST ²⁾ $R_{DS(on)}=1.45 m\Omega$	
				BSC016N06NS ²⁾ $R_{DS(on)}=1.6 m\Omega$	
2-4		IRF7748L1TRPBF $R_{DS(on)}=2.2 m\Omega$		BSC016N06NS ²⁾ $R_{DS(on)}=1.6 m\Omega$	
		BSB028N06NN3 G $R_{DS(on)}=2.8 m\Omega$		BSC019N06NS ²⁾ $R_{DS(on)}=1.9 m\Omega$	
		IRF60DM206 $R_{DS(on)}=2.9 m\Omega$		BSC028N06NS ²⁾ $R_{DS(on)}=2.8 m\Omega$	
				BSC028N06NST ²⁾ $R_{DS(on)}=2.8 m\Omega$	
4-10		IRF7580MTRPBF $R_{DS(on)}=3.6 m\Omega$		BSC031N06NS3 G $R_{DS(on)}=3.1 m\Omega$	
		IRF6648 $R_{DS(on)}=7.0 m\Omega$	BSZ042N06NS ²⁾ $R_{DS(on)}=4.2 m\Omega$	IRLH5036TRPBF $R_{DS(on)}=4.4 m\Omega$	
		IRF6674 $R_{DS(on)}=11.0 m\Omega$		IRFH7545TRPBF $R_{DS(on)}=5.2 m\Omega$	
				BSC034N06NS ²⁾ $R_{DS(on)}=3.4 m\Omega$	
>10				BSC039N06NS ²⁾ $R_{DS(on)}=3.9 m\Omega$	
				BSC066N06NS ²⁾ $R_{DS(on)}=6.6 m\Omega$	
				BSC076N06NS3 G $R_{DS(on)}=7.6 m\Omega$	
				BSC097N06NS ²⁾ $R_{DS(on)}=9.7 m\Omega$	



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$R_{DS(on), max.}$ @ $V_{GS}=10V$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-针)	TO-262 (I ² PAK)	TO-220	裸芯片 ($R_{DS(on)}$ 典型)	PQFN 2 x 2	PQFN 3.3 x 3.3	SuperSO8	SOT-23
1-2		IPB019N06L3 G $R_{DS(on)}=1.9 m\Omega$	IPB016N06L3 G $R_{DS(on)}=1.6 m\Omega$			IPC218N06L3 $R_{DS(on)}=1.2 m\Omega$			BSC014N06LS5 $R_{DS(on)}=1.4 m\Omega$	
		IRL60S216 $R_{DS(on)}=1.95 m\Omega$		IRL60SL216 $R_{DS(on)}=1.95 m\Omega$	IRL60B216 $R_{DS(on)}=1.9 m\Omega$					
2-4		IRLS3036TRLPBF $R_{DS(on)}=2.4 m\Omega$			IRLB3036PBF $R_{DS(on)}=2.4 m\Omega$				BSC027N06LS5 $R_{DS(on)}=2.7 m\Omega$	
	IPD031N06L3 G $R_{DS(on)}=3.1 m\Omega$	IPB034N06L3 G $R_{DS(on)}=3.4 m\Omega$			IPP037N06L3 G $R_{DS(on)}=3.7 m\Omega$				BSC028N06LS3 G $R_{DS(on)}=2.8 m\Omega$	
4-10	IPD048N06L3 G $R_{DS(on)}=4.8 m\Omega$				IPP052N06L3 G $R_{DS(on)}=5.2 m\Omega$			BSZ040N06LS5 $R_{DS(on)}=4.0 m\Omega$	IRLH5036TRPBF $R_{DS(on)}=4.4 m\Omega$	
	IRLR3636TRPBF $R_{DS(on)}=6.8 m\Omega$							BSZ065N06LS5 $R_{DS(on)}=6.5 m\Omega$	BSC065N06LS5 $R_{DS(on)}=6.5 m\Omega$	
	IPD079N06L3 G $R_{DS(on)}=7.9 m\Omega$	IPB081N06L3 G $R_{DS(on)}=8.1 m\Omega$			IPD084N06L3 G $R_{DS(on)}=8.4 m\Omega$	IPP084N06L3 G $R_{DS(on)}=8.4 m\Omega$		BSZ067N06LS3 G $R_{DS(on)}=6.7 m\Omega$	BSC067N06LS3 G $R_{DS(on)}=6.7 m\Omega$	
								BSZ099N06LS5 $R_{DS(on)}=9.9 m\Omega$	BSC094N06LS5 $R_{DS(on)}=9.4 m\Omega$	
>10								BSZ100N06LS3 G $R_{DS(on)}=10.0 m\Omega$	BSC100N06LS3 G $R_{DS(on)}=10.0 m\Omega$	
	IPD350N06L G $R_{DS(on)}=35.0 m\Omega$						IRL60HS118 $R_{DS(on)}=17.0 m\Omega$			IRLML0060 $R_{DS(on)}=92 m\Omega$ IRLML2060 $R_{DS(on)}=480 m\Omega$

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2) 6 V 额定 ($R_{DS(on)}$ 也于 @ $V_{GS} = 6 V$ 规定)



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$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-针)	TO-220	TO-247	裸芯片 ($R_{DS(on)}$ 典型)	DirectFET™	SuperSO8
1-2		IPB020NE7N3 G $R_{DS(on)}=2.0\text{ m}\Omega$	IRFS7730TRL7PP $R_{DS(on)}=2.0\text{ m}\Omega$		IRFP7718PBF $R_{DS(on)}=1.8\text{ m}\Omega$	IPC302NE7N3 $R_{DS(on)}=1.2\text{ m}\Omega$		
2-4		IRFS7730TRLPBF $R_{DS(on)}=2.6\text{ m}\Omega$		IPP023NE7N3 G $R_{DS(on)}=2.3\text{ m}\Omega$				
		IPB031NE7N3 G $R_{DS(on)}=3.1\text{ m}\Omega$	IRFS7734TRL7PP $R_{DS(on)}=3.05\text{ m}\Omega$	IRFB7730PBF $R_{DS(on)}=2.6\text{ m}\Omega$				BSC036NE7NS3 G $R_{DS(on)}=3.6\text{ m}\Omega$
		IRFS7734TRLPBF $R_{DS(on)}=3.5\text{ m}\Omega$		IPP034NE7N3 G $R_{DS(on)}=3.4\text{ m}\Omega$				
4-10		IPB049NE7N3 G $R_{DS(on)}=4.9\text{ m}\Omega$		IPP052NE7N3 G $R_{DS(on)}=5.2\text{ m}\Omega$				BSC042NE7NS3 G $R_{DS(on)}=4.2\text{ m}\Omega$
		IRFS7762TRLPBF $R_{DS(on)}=6.7\text{ m}\Omega$		IPP062NE7N3 G $R_{DS(on)}=6.2\text{ m}\Omega$			IRF7780MTRPBF $R_{DS(on)}=5.7\text{ m}\Omega$	
	IRFR7740TRPBF $R_{DS(on)}=7.2\text{ m}\Omega$			IRFB7740PBF $R_{DS(on)}=7.3\text{ m}\Omega$				
		IRFS7787TRLPBF $R_{DS(on)}=8.4\text{ m}\Omega$		IRFB7787PBF $R_{DS(on)}=8.4\text{ m}\Omega$				IRFH7787TRPBF $R_{DS(on)}=8.0\text{ m}\Omega$
>10	IRFR7746TRPBF $R_{DS(on)}=11.2\text{ m}\Omega$			IRFB7746PBF $R_{DS(on)}=10.6\text{ m}\Omega$			BSF450NE7NH3 ¹⁾ $R_{DS(on)}=45.0\text{ m}\Omega$	



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$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-针)	TO-262 (I ² PAK)	TO-220	TO-220 FullPAK	裸芯片 ($R_{DS(on)}$ 典型)	DirectFET™	PQFN 2 x 2	PQFN 3.3 x 3.3	SuperSO8	TO-无铅
1-2		IPB017N08N5 $R_{DS(on)}=1.7\text{ m}\Omega$	IPB015N08N5 $R_{DS(on)}=1.5\text{ m}\Omega$				IPC302N08N3 $R_{DS(on)}=1.2\text{ m}\Omega$					IPT012N08N5 $R_{DS(on)}=1.2\text{ m}\Omega$
		IPB020N08N5 $R_{DS(on)}=2.0\text{ m}\Omega$	IPB019N08N3 G $R_{DS(on)}=1.9\text{ m}\Omega$		IPP020N08N5 $R_{DS(on)}=2.0\text{ m}\Omega$						BSC021N08NS5 $R_{DS(on)}=2.1\text{ m}\Omega$	IPT019N08N5 $R_{DS(on)}=1.9\text{ m}\Omega$
2-4		IPB024N08N5 $R_{DS(on)}=2.4\text{ m}\Omega$			IPP023N08N5 $R_{DS(on)}=2.3\text{ m}\Omega$						BSC025N08LS5 $R_{DS(on)}=2.5\text{ m}\Omega$	
		IPB025N08N3 G $R_{DS(on)}=2.5\text{ m}\Omega$	IPB030N08N3 G $R_{DS(on)}=3.0\text{ m}\Omega$		IPP027N08N5 $R_{DS(on)}=2.7\text{ m}\Omega$						BSC026N08NS5 $R_{DS(on)}=2.6\text{ m}\Omega$	
					IPP028N08N3 G $R_{DS(on)}=2.8\text{ m}\Omega$	IPA028N08N3 G $R_{DS(on)}=2.8\text{ m}\Omega$					BSC030N08NS5 $R_{DS(on)}=3.0\text{ m}\Omega$	IPT029N08N5 $R_{DS(on)}=2.9\text{ m}\Omega$
		IPB031N08N5 $R_{DS(on)}=3.1\text{ m}\Omega$			IPP034N08N5 $R_{DS(on)}=3.4\text{ m}\Omega$						BSC037N08NS5 $R_{DS(on)}=3.7\text{ m}\Omega$	
											BSC037N08NS5T $R_{DS(on)}=3.7\text{ m}\Omega$	
4-10	IPD046N08N5 $R_{DS(on)}=4.6\text{ m}\Omega$	IPB049N08N5 $R_{DS(on)}=4.9\text{ m}\Omega$			IPP037N08N3 G $R_{DS(on)}=3.7\text{ m}\Omega$	IPA037N08N3 G $R_{DS(on)}=3.7\text{ m}\Omega$					BSC040N08NS5 $R_{DS(on)}=4.0\text{ m}\Omega$	
				IPI037N08N3 G $R_{DS(on)}=3.7\text{ m}\Omega$				BSB044N08NN3 G $R_{DS(on)}=4.4\text{ m}\Omega$			BSC047N08NS3 G $R_{DS(on)}=4.7\text{ m}\Omega$	
	IPD053N08N3 G $R_{DS(on)}=5.3\text{ m}\Omega$	IPB054N08N3 G $R_{DS(on)}=5.4\text{ m}\Omega$			IPP052N08N5 $R_{DS(on)}=5.2\text{ m}\Omega$						BSC052N08NS5 $R_{DS(on)}=5.2\text{ m}\Omega$	
		IPB067N08N3 G $R_{DS(on)}=6.7\text{ m}\Omega$			IPP057N08N3 G $R_{DS(on)}=5.7\text{ m}\Omega$	IPA057N08N3 G $R_{DS(on)}=5.7\text{ m}\Omega$					BSC057N08NS3 G $R_{DS(on)}=5.7\text{ m}\Omega$	
											BSZ070N08LS5 G $R_{DS(on)}=7.0\text{ m}\Omega$	
>10					IPP100N08N3 G $R_{DS(on)}=9.7\text{ m}\Omega$						BSZ075N08NS5 $R_{DS(on)}=7.5\text{ m}\Omega$	BSC061N08NS5 $R_{DS(on)}=6.1\text{ m}\Omega$
											BSZ084N08NS5 $R_{DS(on)}=8.4\text{ m}\Omega$	BSC072N08NS5 $R_{DS(on)}=7.2\text{ m}\Omega$
	IPD096N08N3 G $R_{DS(on)}=9.6\text{ m}\Omega$										BSZ110N08NS5 $R_{DS(on)}=11.0\text{ m}\Omega$	BSC117N08NS5 $R_{DS(on)}=11.7\text{ m}\Omega$
	IPD135N08N3 G $R_{DS(on)}=13.5\text{ m}\Omega$							BSB104N08NP3 $R_{DS(on)}=10.4\text{ m}\Omega$	IRL80HS120 $R_{DS(on)}=32.0\text{ m}\Omega$		BSZ123N08NS3 G $R_{DS(on)}=12.3\text{ m}\Omega$	BSC123N08NS3 G $R_{DS(on)}=12.3\text{ m}\Omega$
										BSZ340N08NS3 G $R_{DS(on)}=34.0\text{ m}\Omega$	BSC340N08NS3 G $R_{DS(on)}=34.0\text{ m}\Omega$	

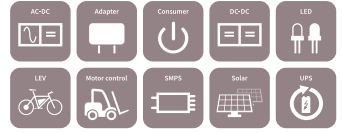
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1) DirectFET™ S

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$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-针)	TO-262 (I ² PAK)	TO-220	TO-220 FullPAK	TO-247
1-2		IPB020N10N5 $R_{DS(on)}=2.0\text{ m}\Omega$	IPB017N10N5 $R_{DS(on)}=1.7\text{ m}\Omega$				IRF100P218 $R_{DS(on)}=1.1\text{ m}\Omega$
		IPB020N10N5LF $R_{DS(on)}=2.0\text{ m}\Omega$	IPB017N10N5LF $R_{DS(on)}=1.7\text{ m}\Omega$				IRF100P219 $R_{DS(on)}=2.1\text{ m}\Omega$
2-4		IPB027N10N3 G $R_{DS(on)}=2.7\text{ m}\Omega$	IPB024N10N5 $R_{DS(on)}=2.4\text{ m}\Omega$		IPP023N10N5 $R_{DS(on)}=2.3\text{ m}\Omega$		IRFP4468PBF $R_{DS(on)}=2.6\text{ m}\Omega$
		IPB027N10N5 $R_{DS(on)}=2.7\text{ m}\Omega$	IPB025N10N3 G $R_{DS(on)}=2.5\text{ m}\Omega$	IPI030N10N3 G $R_{DS(on)}=3.0\text{ m}\Omega$	IPP030N10N3 G $R_{DS(on)}=3.0\text{ m}\Omega$	IPA030N10N3 G $R_{DS(on)}=3.0\text{ m}\Omega$	
		IPB033N10N5LF $R_{DS(on)}=3.3\text{ m}\Omega$	IPB032N10N5 $R_{DS(on)}=3.2\text{ m}\Omega$		IPP030N10N5 $R_{DS(on)}=3.0\text{ m}\Omega$		
			IPB039N10N3 G $R_{DS(on)}=3.9\text{ m}\Omega$		IPP039N10N5 $R_{DS(on)}=3.9\text{ m}\Omega$		
4-10	IPD050N10N5 $R_{DS(on)}=5.0\text{ m}\Omega$	IPB042N10N3 G $R_{DS(on)}=4.2\text{ m}\Omega$		IPI045N10N3 G $R_{DS(on)}=4.5\text{ m}\Omega$	IRFB4110PBF $R_{DS(on)}=4.5\text{ m}\Omega$	IPA045N10N3 G $R_{DS(on)}=4.5\text{ m}\Omega$	IRFP4110PBF $R_{DS(on)}=4.5\text{ m}\Omega$
	IPD068N10N3 G $R_{DS(on)}=6.8\text{ m}\Omega$	IRFS4010TRLPBF $R_{DS(on)}=4.7\text{ m}\Omega$			IPP045N10N3 G $R_{DS(on)}=4.5\text{ m}\Omega$	IPA083N10N5 $R_{DS(on)}=8.3\text{ m}\Omega$	IRFP4310ZPBF $R_{DS(on)}=6.0\text{ m}\Omega$
		IPB065N10N3 G $R_{DS(on)}=6.5\text{ m}\Omega$			IRFB4310ZPBF $R_{DS(on)}=6.0\text{ m}\Omega$	IPA086N10N3 G $R_{DS(on)}=8.6\text{ m}\Omega$	
		IRFS4310ZTRLPBF $R_{DS(on)}=7.0\text{ m}\Omega$					
				IPI072N10N3 G $R_{DS(on)}=7.2\text{ m}\Omega$	IPP072N10N3 G $R_{DS(on)}=7.2\text{ m}\Omega$		
	IPD082N10N3 G $R_{DS(on)}=8.2\text{ m}\Omega$				IPP083N10N5 $R_{DS(on)}=8.3\text{ m}\Omega$		
		IPB083N10N3 G $R_{DS(on)}=8.3\text{ m}\Omega$		IPI086N10N3 G $R_{DS(on)}=8.6\text{ m}\Omega$	IPP086N10N3 G $R_{DS(on)}=8.6\text{ m}\Omega$		
	IRFS4410ZTRLPBF $R_{DS(on)}=9.0\text{ m}\Omega$			IRFS4410ZTRLPBF $R_{DS(on)}=9.0\text{ m}\Omega$		IRFP4410ZPBF $R_{DS(on)}=9.0\text{ m}\Omega$	
10-25	IPD122N10N3 G $R_{DS(on)}=12.2\text{ m}\Omega$						
	IPD12CN10N G $R_{DS(on)}=12.4\text{ m}\Omega$	IPB123N10N3 G $R_{DS(on)}=12.3\text{ m}\Omega$					
	IRFR4510TRPBF $R_{DS(on)}=13.9\text{ m}\Omega$	IRFS4510TRLPBF $R_{DS(on)}=13.9\text{ m}\Omega$					
	IPD180N10N3 G $R_{DS(on)}=18.0\text{ m}\Omega$			IPI180N10N3 G $R_{DS(on)}=18.0\text{ m}\Omega$			
	IPD25CN10N G $R_{DS(on)}=25.0\text{ m}\Omega$						
>25	IPD33CN10N G $R_{DS(on)}=33.0\text{ m}\Omega$						
	IPD78CN10N G $R_{DS(on)}=78.0\text{ m}\Omega$						



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$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	裸芯片 ($R_{DS(on)}$ 典型)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	SO-8	TO-无铅
1-2	IPC302N10N3 $R_{DS(on)}=1.7\text{ m}\Omega$					IPT015N10N5 $R_{DS(on)}=1.5\text{ m}\Omega$
	IPC313N10N3R $R_{DS(on)}=1.9\text{ m}\Omega$			BSC027N10NS5 $R_{DS(on)}=2.7\text{ m}\Omega$		IPT020N10N3 $R_{DS(on)}=2.0\text{ m}\Omega$ IPT020N10N5 $R_{DS(on)}=2.0\text{ m}\Omega$
2-4	IPC26N10NR $R_{DS(on)}=3.2\text{ m}\Omega$	IRF7769L1TRPBF $R_{DS(on)}=3.5\text{ m}\Omega$		BSC035N10NS5 $R_{DS(on)}=3.5\text{ m}\Omega$		IPT026N10N5 $R_{DS(on)}=2.6\text{ m}\Omega$
	IPC173N10N3 $R_{DS(on)}=3.6\text{ m}\Omega$			BSC040N10NS5 $R_{DS(on)}=4.0\text{ m}\Omega$		
4-10		IRF100DM116 ³⁾ $R_{DS(on)}=4.3\text{ m}\Omega$		BSC050N10N5 $R_{DS(on)}=5.0\text{ m}\Omega$		
		BSB056N10NN3 G $R_{DS(on)}=5.6\text{ m}\Omega$		BSC060N10NS3 G $R_{DS(on)}=6.0\text{ m}\Omega$		
				BSC070N10NS3 G $R_{DS(on)}=7.0\text{ m}\Omega$		
				BSC070N10NS5 $R_{DS(on)}=7.0\text{ m}\Omega$		
				IRFH5010TRPBF $R_{DS(on)}=9.0\text{ m}\Omega$		
10-25			BSZ097N10NS5 $R_{DS(on)}=9.7\text{ m}\Omega$	BSC098N10NS5 $R_{DS(on)}=9.8\text{ m}\Omega$		
				BSC109N10NS3 G $R_{DS(on)}=10.9\text{ m}\Omega$		
		BSF134N10NJ3 G ¹⁾ $R_{DS(on)}=13.4\text{ m}\Omega$		BSC118N10NS G $R_{DS(on)}=11.8\text{ m}\Omega$		
	IPC045N10N3 $R_{DS(on)}=15.2\text{ m}\Omega$		BSZ160N10NS3 G $R_{DS(on)}=16.0\text{ m}\Omega$	BSC160N10NS3 G $R_{DS(on)}=16.0\text{ m}\Omega$		
		IRF6662TRPBF $R_{DS(on)}=22.0\text{ m}\Omega$		BSC196N10NS G $R_{DS(on)}=19.6\text{ m}\Omega$	IRF7853TRPBF $R_{DS(on)}=18.0\text{ m}\Omega$	
>25		IRF6645TRPBF $R_{DS(on)}=35.0\text{ m}\Omega$	BSZ440N10NS3 G $R_{DS(on)}=44.0\text{ m}\Omega$	BSC252N10NSFG $R_{DS(on)}=25.2\text{ m}\Omega$		
		IRF7665S2TRPBF $R_{DS(on)}=62.0\text{ m}\Omega$		BSC440N10NS3 G $R_{DS(on)}=44.0\text{ m}\Omega$		
2 x 75				BSC750N10ND G $R_{DS(on)}=75.0\text{ m}\Omega$; 双		
2 x 195			IRFHM792TRPBF $R_{DS(on)}=195.0\text{ m}\Omega$			

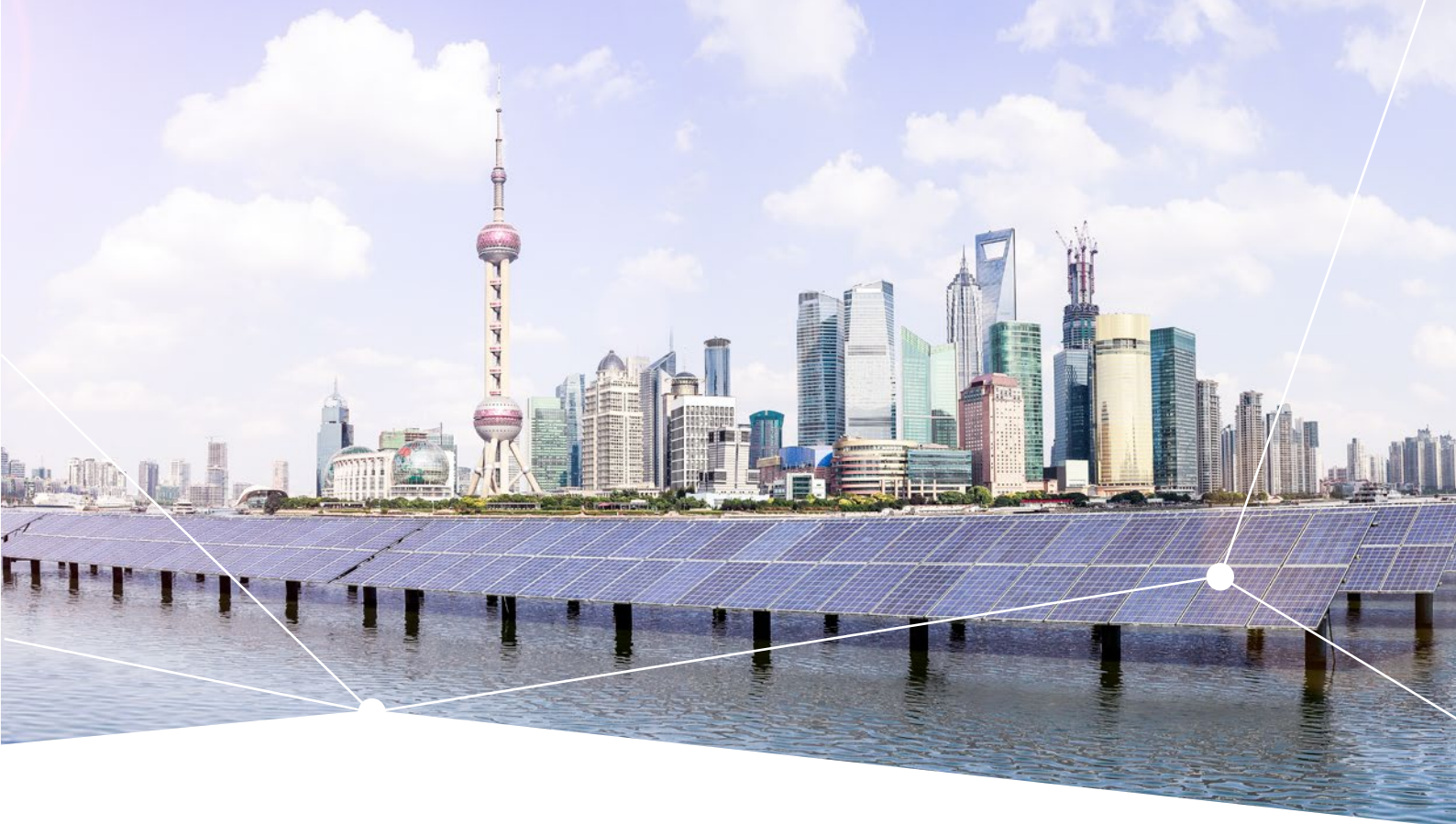
OptiMOS™ 和 StrongIRFET™ 100 V 逻辑电平



$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-针)	TO-220	裸芯片 ($R_{DS(on)}$ 典型)	PQFN 2 x 2	PQFN 3.3 x 3.3	SuperSO8	SOT-23
2-4			IRLS4030TRL7PP $R_{DS(on)}=3.9\text{ m}\Omega$					BSC034N10LS5 $R_{DS(on)}=3.4\text{ m}\Omega$	
4-10		IRLS4030TRLPBF $R_{DS(on)}=4.3\text{ m}\Omega$		IRLB4030PBF $R_{DS(on)}=4.3\text{ m}\Omega$			BSZ096N10LS5 $R_{DS(on)}=9.6\text{ m}\Omega$		
10-25				IPP12CN10L G $R_{DS(on)}=12.0\text{ m}\Omega$	IPC045N10L3 ²⁾ $R_{DS(on)}=16.0\text{ m}\Omega$		BSZ146N10LS5 $R_{DS(on)}=14.6\text{ m}\Omega$	BSC123N10LS G $R_{DS(on)}=12.3\text{ m}\Omega$	
	IRLR3110ZTRPBF $R_{DS(on)}=14.0\text{ m}\Omega$						BSZ150N10LS3 $R_{DS(on)}=15.0\text{ m}\Omega$	BSC146N10LS5 $R_{DS(on)}=14.6\text{ m}\Omega$	
>25					IPC020N10L3 ³⁾ $R_{DS(on)}=42.0\text{ m}\Omega$	IRL100HS121 $R_{DS(on)}=42.0\text{ m}\Omega$		BSC265N10LSFG $R_{DS(on)}=26.5\text{ m}\Omega$	IRLML0100 $R_{DS(on)}=220\text{ m}\Omega$

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1) DirectFET™ S
2) $R_{DS(on)}$ 典型@ 4.5 V
3) 即将发布



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$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-针)	TO-262 (I ² PAK)	TO-220	裸芯片 ($R_{DS(on)}$ 典型)	PQFN 3.3 x 3.3	SuperSO8
2-4						IPC302N12N3 $R_{DS(on)}=2.5\text{ m}\Omega$		
						IPC26N12N $R_{DS(on)}=3.0\text{ m}\Omega$		
		IPB038N12N3 G $R_{DS(on)}=3.8\text{ m}\Omega$	IPB036N12N3 G $R_{DS(on)}=3.6\text{ m}\Omega$			IPC26N12NR $R_{DS(on)}=3.2\text{ m}\Omega$		
4-10				IPI041N12N3 G $R_{DS(on)}=4.1\text{ m}\Omega$	IPP041N12N3 G $R_{DS(on)}=4.1\text{ m}\Omega$			
					IPP048N12N3 G $R_{DS(on)}=4.8\text{ m}\Omega$			
				IPI076N12N3 G $R_{DS(on)}=7.6\text{ m}\Omega$	IPP076N12N3 G $R_{DS(on)}=7.6\text{ m}\Omega$			BSC077N12NS3 G $R_{DS(on)}=7.7\text{ m}\Omega$
10-25	IPD110N12N3 G $R_{DS(on)}=11.0\text{ m}\Omega$				IPP114N12N3 G $R_{DS(on)}=11.4\text{ m}\Omega$			
		IPB144N12N3 G $R_{DS(on)}=14.4\text{ m}\Omega$		IPI147N12N3 G $R_{DS(on)}=14.7\text{ m}\Omega$	IPP147N12N3 G $R_{DS(on)}=14.7\text{ m}\Omega$		BSZ240N12NS3 G $R_{DS(on)}=24.0\text{ m}\Omega$	BSC190N12NS3 G $R_{DS(on)}=19.0\text{ m}\Omega$



OptiMOS™ 和 StrongIRFET™ 135-150 V 正常电平

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	裸芯片 ($R_{DS(on)}$ 典型)	DirectFET™	PQFN 3.3 x 3.3	SupersO8	TO-无铅
4-10	IPC302N15N3 $R_{DS(on)}=4.9\text{ m}\Omega$			BSC093N15NS5 $R_{DS(on)}=9.3\text{ m}\Omega$	IPT059N15N3 $R_{DS(on)}=5.9\text{ m}\Omega$
	IPC300N15N3R $R_{DS(on)}=4.9\text{ m}\Omega$				
10-25		IRF7779L2TRPBF ⁵⁾ $R_{DS(on)}=11.0\text{ m}\Omega$		BSC110N15NS5 $R_{DS(on)}=11.0\text{ m}\Omega$	
				BSC160N15NS5 $R_{DS(on)}=16.0\text{ m}\Omega$	
>25		BSB165N15N3 G $R_{DS(on)}=16.5\text{ m}\Omega$		BSC190N15NS3 G $R_{DS(on)}=19.0\text{ m}\Omega$	
		BSB280N15N3 G $R_{DS(on)}=28.0\text{ m}\Omega$	BSZ300N15NS5 $R_{DS(on)}=30.0\text{ m}\Omega$	BSC360N15NS3 G $R_{DS(on)}=36.0\text{ m}\Omega$	
		IRF6643TRPBF $R_{DS(on)}=34.5\text{ m}\Omega$	BSZ520N15NS3 G $R_{DS(on)}=52.0\text{ m}\Omega$	BSC520N15NS3 G $R_{DS(on)}=52.0\text{ m}\Omega$	
		IRF6775MTRPBF $R_{DS(on)}=56.0\text{ m}\Omega$	BSZ900N15NS3 G $R_{DS(on)}=90.0\text{ m}\Omega$		



OptiMOS™ 和 StrongIRFET™ 135-150 V 正常电平

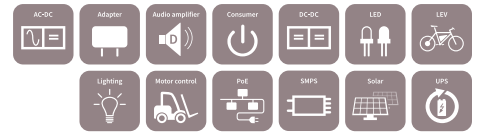
$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK 7-针)	TO-263 (D ² PAK 7-针+)	TO-251/ TO-251 短导线 (IPAK/IPAK 短 导线)	TO-262 (I ² PAK)	TO-220	TO-220 FullPAK	TO-247
4-10		IPB048N15N5 $R_{DS(on)}=4.8\text{ m}\Omega$	IPB044N15N5 $R_{DS(on)}=4.4\text{ m}\Omega$			IPI051N15N5 $R_{DS(on)}=5.1\text{ m}\Omega$	IPP051N15N5 ²⁾ $R_{DS(on)}=5.1\text{ m}\Omega$		IRF150P220 $R_{DS(on)}=2.5\text{ m}\Omega$
		IPB048N15N5LF $R_{DS(on)}=4.8\text{ m}\Omega$	IRF135SA204 ⁵⁾ $R_{DS(on)}=5.9\text{ m}\Omega$	IRF135SA204 $R_{DS(on)}=5.9\text{ m}\Omega$					IRF150P221 $R_{DS(on)}=4.8\text{ m}\Omega$
		IPB072N15N3 G $R_{DS(on)}=7.2\text{ m}\Omega$	IPB060N15N5 $R_{DS(on)}=6.0\text{ m}\Omega$			IPI075N15N3 G $R_{DS(on)}=7.5\text{ m}\Omega$	IPP075N15N3 G $R_{DS(on)}=7.5\text{ m}\Omega$		IRFP4568PBF $R_{DS(on)}=5.9\text{ m}\Omega$
		IPB073N15N5 $R_{DS(on)}=7.3\text{ m}\Omega$	IPB065N15N3 G $R_{DS(on)}=6.5\text{ m}\Omega$			IPI076N15N5 $R_{DS(on)}=7.6\text{ m}\Omega$	IPP076N15N5 $R_{DS(on)}=7.6\text{ m}\Omega$	IPA075N15N3 G $R_{DS(on)}=7.5\text{ m}\Omega$	
		IPB083N15N5LF $R_{DS(on)}=8.3\text{ m}\Omega$							
			IRF135S203 ⁵⁾ $R_{DS(on)}=8.4\text{ m}\Omega$					IRF135B203 ⁵⁾ $R_{DS(on)}=8.4\text{ m}\Omega$	
10-25		IPB108N15N3 G $R_{DS(on)}=10.8\text{ m}\Omega$	IRFS4115TRL7PP $R_{DS(on)}=11.8\text{ m}\Omega$			IPI111N15N3 G $R_{DS(on)}=11.1\text{ m}\Omega$	IPP111N15N3 G $R_{DS(on)}=11.1\text{ m}\Omega$	IPA105N15N3 G $R_{DS(on)}=10.5\text{ m}\Omega$	
		IRFS4321 $R_{DS(on)}=15.0\text{ m}\Omega$	IRFS4321TRL7PP $R_{DS(on)}=14.7\text{ m}\Omega$				IRFB4321PBF $R_{DS(on)}=15.0\text{ m}\Omega$		IRFP4321PBF $R_{DS(on)}=15.5\text{ m}\Omega$
	IPD200N15N3 G $R_{DS(on)}=20.0\text{ m}\Omega$	IPB200N15N3 G $R_{DS(on)}=20.0\text{ m}\Omega$					IPP200N15N3 G ²⁾ $R_{DS(on)}=20.0\text{ m}\Omega$		
>25		IRFS4615PBF $R_{DS(on)}=42.0\text{ m}\Omega$					IRFB4615PBF $R_{DS(on)}=39.0\text{ m}\Omega$		
	IRFR4615 $R_{DS(on)}=42.0\text{ m}\Omega$	IRFS5615PBF $R_{DS(on)}=42.0\text{ m}\Omega$		IRFU4615PBF $R_{DS(on)}=42.0\text{ m}\Omega$			IRFB5615PBF $R_{DS(on)}=39.0\text{ m}\Omega$		
	IPD530N15N3 G $R_{DS(on)}=53.0\text{ m}\Omega$	IPB530N15N3 G $R_{DS(on)}=53.0\text{ m}\Omega$				IPI530N15N3 G ²⁾ $R_{DS(on)}=53.0\text{ m}\Omega$	IPP530N15N3 G ²⁾ $R_{DS(on)}=53.0\text{ m}\Omega$		
							IRFB4019PBF $R_{DS(on)}=95.0\text{ m}\Omega$		

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2) 8 V 额定 ($R_{DS(on)}$ 也于 @ $V_{GS} = 8\text{ V}$ 规定)

3) 开发中

5) 135 V



OptiMOS™ 和 StrongIRFET™ 200 V 正常电平

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-263 (D ² PAK+)	TO-262 (I ² PAK)	TO-220	TO-247
4-10						IRF200P222 $R_{DS(on)}=6.6\text{ m}\Omega$ IRFP4668PBF $R_{DS(on)}=9.7\text{ m}\Omega$
10-25		IPB107N20N3 G $R_{DS(on)}=10.7\text{ m}\Omega$	IRF200S234 $R_{DS(on)}=16.9\text{ m}\Omega$	IPI110N20N3 G $R_{DS(on)}=11.0\text{ m}\Omega$	IPP110N20N3 G $R_{DS(on)}=11.0\text{ m}\Omega$	IRF200P223 $R_{DS(on)}=11.5\text{ m}\Omega$
		IPB107N20NA ⁴⁾ $R_{DS(on)}=10.7\text{ m}\Omega$				
		IPB110N20N3LF $R_{DS(on)}=11.0\text{ m}\Omega$			IPP120N20NFD $R_{DS(on)}=12.0\text{ m}\Omega$	IRFP4127PBF $R_{DS(on)}=21.0\text{ m}\Omega$
		IPB117N20NFD $R_{DS(on)}=11.7\text{ m}\Omega$			IRFB4127PBF $R_{DS(on)}=20.0\text{ m}\Omega$	IRFP4227PBF $R_{DS(on)}=25.0\text{ m}\Omega$
		IPB156N22NFD ²⁾ $R_{DS(on)}=15.6\text{ m}\Omega$				
>25		IRFS4127TRLPBF $R_{DS(on)}=22.0\text{ m}\Omega$				
		IRFS4227TRLPBF $R_{DS(on)}=26.0\text{ m}\Omega$			IRFB4227PBF $R_{DS(on)}=26.0\text{ m}\Omega$	
	IPD320N20N3 G $R_{DS(on)}=32.0\text{ m}\Omega$	IPB320N20N3 G $R_{DS(on)}=32.0\text{ m}\Omega$		IPI320N20N3 G $R_{DS(on)}=32.0\text{ m}\Omega$	IPP320N20N3 G $R_{DS(on)}=32.0\text{ m}\Omega$	
	IRFR4620TRLPBF $R_{DS(on)}=78.0\text{ m}\Omega$	IRFS4620TRLPBF $R_{DS(on)}=78.0\text{ m}\Omega$			IRFB4620PBF $R_{DS(on)}=72.5\text{ m}\Omega$	
		IRFS4020TRLPBF $R_{DS(on)}=105.0\text{ m}\Omega$			IRFB5620PBF $R_{DS(on)}=72.5\text{ m}\Omega$ IRFB4020PBF $R_{DS(on)}=100.0\text{ m}\Omega$ IRF200B211 $R_{DS(on)}=170.0\text{ m}\Omega$	

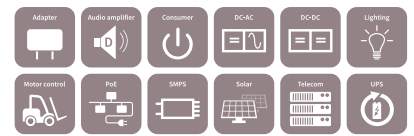


OptiMOS™ 和 StrongIRFET™ 200 V 正常电平

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	裸芯片 ($R_{DS(on)}$ 典型)	DirectFET™	PQFN 3.3 x 3.3	SuperSO8	SO-8	TO-无铅	TO-247
4-10	IPC300N20N3 $R_{DS(on)}=9.2\text{ m}\Omega$ IPC302N20N3 $R_{DS(on)}=9.2\text{ m}\Omega$						IRF200P222 $R_{DS(on)}=6.6\text{ m}\Omega$
10-25	IPC302N20NFD $R_{DS(on)}=9.4\text{ m}\Omega$			BSC220N20NSFD $R_{DS(on)}=22.0\text{ m}\Omega$		IPT111N20NFD $R_{DS(on)}=11.1\text{ m}\Omega$	IRF200P223 $R_{DS(on)}=11.5\text{ m}\Omega$
>25				BSC320N20NS3 G $R_{DS(on)}=32.0\text{ m}\Omega$ BSC350N20NSFD $R_{DS(on)}=35.0\text{ m}\Omega$ BSC500N20NS3G $R_{DS(on)}=50.0\text{ m}\Omega$			
		IRF6641TRPBF $R_{DS(on)}=59.9\text{ m}\Omega$		IRFH5020 $R_{DS(on)}=55.0\text{ m}\Omega$			
			BSZ900N20NS3 G $R_{DS(on)}=90.0\text{ m}\Omega$	BSC900N20NS3 G $R_{DS(on)}=90.0\text{ m}\Omega$	IRF7820TRPBF $R_{DS(on)}=78.0\text{ m}\Omega$		
		IRF6785TRPBF $R_{DS(on)}=100.0\text{ m}\Omega$	BSZ12DN20NS3 G $R_{DS(on)}=125.0\text{ m}\Omega$	BSC12DN20NS3 G $R_{DS(on)}=125.0\text{ m}\Omega$			
			BSZ22DN20NS3 G $R_{DS(on)}=225.0\text{ m}\Omega$	BSC22DN20NS3 G $R_{DS(on)}=225.0\text{ m}\Omega$			

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2) 220 V 额定
3) 开发中
4) 零件符合 AEC Q101



OptiMOS™ 和 StrongIRFET™ 250 V 正常电平

$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-262 (I ² PAK)	TO-220	TO-247	裸芯片 ($R_{DS(on)}$ 典型)	PQFN 3.3 x 3.3	SuperSO8	TO-无铅
10-25		IPB200N25N3 G $R_{DS(on)}=20.0\text{ m}\Omega$	IPI200N25N3 G $R_{DS(on)}=20.0\text{ m}\Omega$	IPP200N25N3 G $R_{DS(on)}=20.0\text{ m}\Omega$	IRF250P224 $R_{DS(on)}=12.0\text{ m}\Omega$				
				IPP220N25NFD $R_{DS(on)}=22.0\text{ m}\Omega$	IRFP4768PBF $R_{DS(on)}=17.5\text{ m}\Omega$	IPC302N25N3 $R_{DS(on)}=16.0\text{ m}\Omega$			IPT210N25NFD $R_{DS(on)}=21.0\text{ m}\Omega$
					IRF250P225 $R_{DS(on)}=22.0\text{ m}\Omega$				
>25								BSC430N25NSFD $R_{DS(on)}=43.0\text{ m}\Omega$	
		IRFS4229TRL PBF $R_{DS(on)}=48.0\text{ m}\Omega$		IRFB4332PBF $R_{DS(on)}=33.0\text{ m}\Omega$	IRFP4332PBF $R_{DS(on)}=33.0\text{ m}\Omega$			BSC600N25NS3 G $R_{DS(on)}=60.0\text{ m}\Omega$	
								BSC670N25NSFD $R_{DS(on)}=67.0\text{ m}\Omega$	
		IPD600N25N3 G $R_{DS(on)}=60.0\text{ m}\Omega$	IPB600N25N3 G $R_{DS(on)}=60.0\text{ m}\Omega$	IPI600N25N3 G $R_{DS(on)}=60.0\text{ m}\Omega$	IRFB4229PBF $R_{DS(on)}=46.0\text{ m}\Omega$	IRFP4229PBF $R_{DS(on)}=46.0\text{ m}\Omega$		BSZ16DN25NS3 G $R_{DS(on)}=165.0\text{ m}\Omega$	IRFH5025 $R_{DS(on)}=100.0\text{ m}\Omega$
				IPP600N25N3 G $R_{DS(on)}=60.0\text{ m}\Omega$		IPC045N25N3 $R_{DS(on)}=146.0\text{ m}\Omega$	BSZ42DN25NS3 G $R_{DS(on)}=425.0\text{ m}\Omega$	BSC16DN25NS3 G $R_{DS(on)}=165.0\text{ m}\Omega$	

OptiMOS™ 和 StrongIRFET™ 300 V 正常电平



$R_{DS(on), max.}$ @ $V_{GS}=10\text{ V}$ [mΩ]	TO-263 (D ² PAK)	TO-220	TO-247	SuperSO8
0-25			IRF300P226 $R_{DS(on)}=19.0\text{ m}\Omega$	
>25	IPB407N30N $R_{DS(on)}=40.7\text{ m}\Omega$	IPP410N30N $R_{DS(on)}=41.0\text{ m}\Omega$	IRFP4868PBF $R_{DS(on)}=32.0\text{ m}\Omega$	
			IRF300P227 $R_{DS(on)}=40.0\text{ m}\Omega$	
		IRFB4137PBF $R_{DS(on)}=69.0\text{ m}\Omega$	IRFP4137PBF $R_{DS(on)}=69.0\text{ m}\Omega$	BSC13DN30NSFD $R_{DS(on)}=130.0\text{ m}\Omega$

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小信号 P-沟道



电压 [V]	SOT-223	TSOP-6	SOT-89	SC59	SOT-23	SOT-323	SOT-363	
-250	BSP317P 4 Ω, -0.43 A, LL		BSS192P 12 Ω, -0.19 A, LL	BSR92P 11 Ω, -0.14 A, LL				
	BSP92P 12 Ω, -0.26 A, LL							
-100	BSP321P 900 mΩ, -0.98 A, NL							
	BSP322P 800 mΩ, -1.0 A, LL							
-60	BSP316P 1.8 Ω, -0.68 A, LL			BSR316P 1.8 Ω, -0.36 A, LL				
	BSP612P 120 mΩ, 3 A, LL				ISS17EP06LM 1.7Ω, -0.3 A, LL			
	BSP613P 130 mΩ, 2.9 A, NL				BSS83P 2 Ω, -0.33 A, LL	BSS84PW 8 Ω, -0.15 A, LL		
	BSP170P 300 mΩ, -1.9 A, NL				ISS55EP06LM 5.5 Ω, -0.18 A, NL			
	BSP171P 300 mΩ, -1.9 A, LL				BSS84P 8 Ω, -0.17 A, LL			
	BSP315P 800 mΩ, -1.17 A, LL							
	ISP650P06NM 65 mΩ, -3.7 A, NL			BSR315P 800 mΩ, -0.62 A, LL				
	ISP12DP06NM 125 mΩ, -2.8, NL							
	ISP25DP06LM 250 mΩ, -1.9 A, LL							
	ISP25DP06NM 250 mΩ, -1.9 A, NL							
	ISP75DP06LM 750 mΩ, -1.1 A, LL							
		BSL303SPE 33 mΩ, -6.3 A, LL				BSS308PE 80 mΩ, -2.1 A, LL, ESD		BSD314SPE 140 mΩ, -1.5 A, LL, ESD
		IRFTS9342TRPBF* 40 mΩ, -5.8 A, LL				BSS314PE 140 mΩ, -1.5 A, LL, ESD		
	-30		BSL307SP 43 mΩ, -5.5 A, LL			BSS315P 150 mΩ, -1.5 A, LL		
		BSL305SPE 45 mΩ, -5.5 A, LL						
		BSL308PE 80 mΩ, -2.1 A, LL, 双, ESD						
		BSL314PE 140 mΩ, -1.5 A, LL, ESD, 双						
-20		BSL207SP 41 mΩ, -6 A, SLL			IRLML2244* 1) 54 mΩ, 4.3 A, LL			
		BSL211SP 67 mΩ, -4.7 A, SLL			IRLML2246* 1) 135 mΩ, 2.6 A, LL	BSS209PW 550 mΩ, -0.58 A, SLL	BSV236SP 175 mΩ, -1.5 A, SLL	
				BSS215P 150 mΩ, -1.5 A, SLL	BSS223PW 1.2 Ω, -0.39 A, SLL	BSD223P 1.2 Ω, -0.39 A, SLL, 双		

互补小信号



电压 [V]	SOT-223	TSOP-6	SOT-89	SC59	SOT-23	SOT-323	SOT-363
-20/20		BSL215C N: 140 mΩ, 1.5 A, SLL P: 150 mΩ, 1.5 A, SLL					BSD235C N: 350 mΩ, 0.95 A, SLL P: 1.2 Ω, 0.53 A, SLL
-30/30		BSL308C N: 57 mΩ, 2.3 A, LL P: 80 mΩ, -2.0 A, LL					
		BSL316C N: 160 mΩ, 1.4 A, LL P: 150 mΩ, -1.5 A, LL					

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所有产品均符合汽车AEC Q101 (标有*的零件除外)

1) R_{DS(on)} 4.5 V 额定

小信号 N-沟道



电压 [V]	SOT-223	TSOP-6	SOT-89	SC59	SOT-23	SOT-323	SOT-363	
20		BSL802SN 22 mΩ, 7.5 A, ULL		BSR802N 23 mΩ, 3.7 A, ULL	IRLML6244* ¹⁾ 21 mΩ, 6.3 A, LL			
		BSL202SN 22 mΩ, 7.5 A, SLL		BSR202N 21 mΩ, 3.8 A, SLL	IRLML6246* ¹⁾ 46 mΩ, 4.1 A, LL			
		BSL205N 50 mΩ, 2.5 A, SLL, 双			BSS205N 50 mΩ, 2.5 A, SLL		BSD214SN 140 mΩ, 1.5 A, SLL	
					BSS806NE 57 mΩ, 2.3 A, ULL, ESD		BSD816SN 160 mΩ, 1.4 A, ULL	
		BSL207N 70 mΩ, 2.1 A, SLL, 双			BSS806N 57 mΩ, 2.3 A, ULL	BSS214NW 140 mΩ, 1.5 A, SLL	BSD235N 350 mΩ, 0.95 A, SLL, 双	
		BSL214N 140 mΩ, 1.5 A, SLL, 双			BSS214N 140 mΩ, 1.5 A, SLL	BSS816NW 160 mΩ, 1.4 A, ULL	BSD840N 400 mΩ, 0.88 A, ULL, 双	
25					IRFML8244* 24 mΩ, 5.8 A, NL			
30		IRLTS6342* ¹⁾ 17.5 mΩ, 8.3 A, LL		BSR302N 23 mΩ, 3.7 A, LL	IRLML0030* 27 mΩ, 5.3 A, LL		BSD316SN 160 mΩ, 1.4 A, LL	
		IRFTS8342* 19 mΩ, 8.2 A, NL			IRLML6344* ¹⁾ 29 mΩ, 5.0 A, LL			
		BSL302SN 25 mΩ, 7.1 A, LL			BSS306N 57 mΩ, 2.3 A, LL			
		BSL306N 57 mΩ, 2.3 A, LL, 双			IRLML6346* ¹⁾ 63 mΩ, 3.4 A, LL			
55					IRLML2030* 100 mΩ, 1.4 A, LL			
					BSS316N 160 mΩ, 1.4 A, LL			
					BSS67052L 650 mΩ, 0.54 A, LL	BSS340NW 400 mΩ, 0.88 A, LL		
		BSP318S 90 mΩ, 2.6 A, LL	BSL606SN 60 mΩ, 4.5 A, LL	BSS606N 60 mΩ, 3.2 A, LL	BSR606N 60 mΩ, 2.3 A, LL	IRLML0060* 92 mΩ, 2.7 A, LL	BSS138W 3.5 Ω, 0.28 A, LL	2N7002DW 3 Ω, 0.3 A, LL, 双
		BSP320S 120 mΩ, 2.9 A, NL				IRLML2060* 480 mΩ, 1.2 A, LL	SN7002W 5 Ω, 0.23 A, LL	
		BSP295 300 mΩ, 1.8 A, LL				BSS138N 3.5 Ω, 0.23 A, LL		
60					BSS7728N 5 Ω, 0.2 A, LL			
					SN7002N 5 Ω, 0.2 A, LL			
					2N7002 3 Ω, 0.3 A, LL			
					BSS159N 8 Ω, 0.13 A, 已部署			
		BSP716N 160 mΩ, 2.3 A, LL	BSL716SN 150 mΩ, 2.5 A, LL					
75								
80								
100	BSP372N 230 mΩ, 1.8 A, LL	BSL372SN 220 mΩ, 2.0 A, LL			IRLML0100* 220 mΩ, 1.6 A, LL			
	BSP373N 240 mΩ, 1.8 A, NL	BSL373SN 230 mΩ, 2.0 A, NL			BSS119N 6 Ω, 0.19 A, LL			
	BSP296N 600 mΩ, 1.2 A, LL	BSL296SN 460 mΩ, 1.4 A, LL			V _{GS(on)} 1.8 V 至 2.3 V BSS123N 6 Ω, 0.19 A, LL			
200					V _{GS(on)} 0.8 V 至 1.8 V BSS169 12 Ω, 0.09 A, 已部署			
	BSP297 1.8 Ω, 0.66 A, LL							
	BSP149 3.5 Ω, 0.14 A, 已部署							
240	BSP88 6 Ω, 0.35 A, 2.8 V 额定		BSS87 6 Ω, 0.26 A, LL		BSS131 14 Ω, 0.1 A, LL			
	BSP89 6 Ω, 0.35 A, LL							
	BSP129 6 Ω, 0.05 A, 已部署							
250					BSS139 30 Ω, 0.03 A, 已部署			
400	BSP298 3 Ω, 0.5 A, NL							
	BSP179 24 Ω, 0.04 A, 已部署							
	BSP324 25 Ω, 0.17 A, LL							
500	BSP299 4 Ω, 0.4 A, NL							
600	BSP125 45 Ω, 0.12 A, LL		BSS225 45 Ω, 0.09 A, LL		BSS127 500 Ω, 0.023 A, LL			
	BSP135 60 Ω, 0.02 A, 已部署				BSS126 700 Ω, 0.007 A, 已部署			
800	BSP300 20 Ω, 0.19 A, NL							

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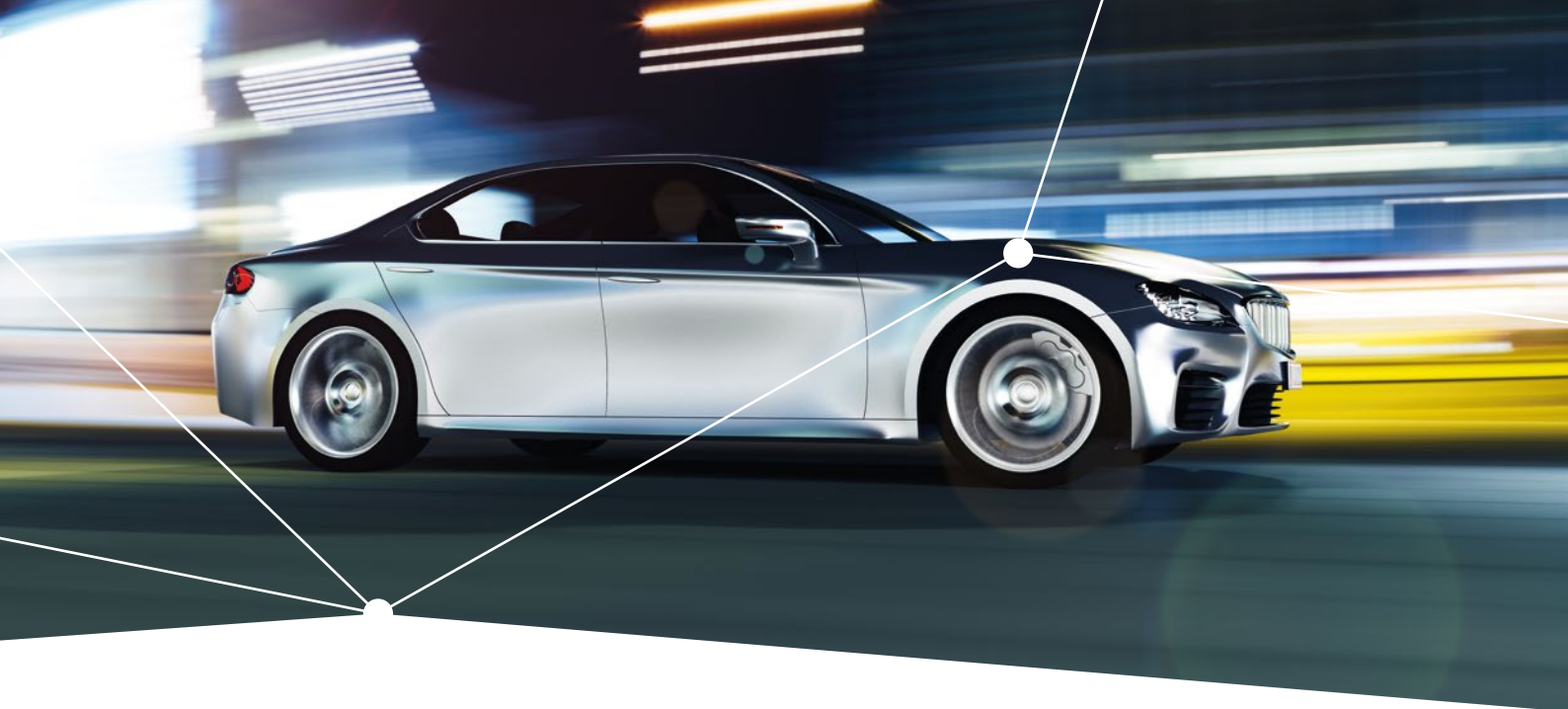
所有产品均符合汽车AEC Q101 (2N7002除外) (标有*的零件除外)

1) R_{DS(on)} 于 4.5 V 规定

功率 P-沟道MOSFET



电压 [V]	TO-252 (DPAK)	DirectFET™	SOT-23	PQFN 3.3 x 3.3	SuperSO8	SO-8	PQFN 2 x 2	TSOP-6
-20						BSO201SP H R _{DS(on)} =7.0 mΩ		
						BSO203SP H R _{DS(on)} =21.0 mΩ		
						BSO203P H R _{DS(on)} =21.0 mΩ		
				IRLML2244 ²⁾ *** R _{DS(on)} =54 mΩ			IRLHS2242TRPBF** R _{DS(on)} =31.0 mΩ	IRLTS2242 R _{DS(on)} =39 mΩ
				IRLML2246 ²⁾ *** R _{DS(on)} =135 mΩ			BSO207P H R _{DS(on)} =45.0 mΩ	
-30						BSO211P H R _{DS(on)} =67.0 mΩ		
	IPD042P03L3 G R _{DS(on)} =4.2 mΩ				BSC030P03NS3 G R _{DS(on)} =3.0 mΩ BSC060P03NS3E G R _{DS(on)} =6.0 mΩ; ESD	IRF9310 R _{DS(on)} =4.6 mΩ IRF9317 R _{DS(on)} =6.6 mΩ		
	SPD50P03L G ¹⁾ * R _{DS(on)} =7.0 mΩ	IRF9395M R _{DS(on)} =7.0 mΩ; 双		BSZ086P03NS3 G R _{DS(on)} =8.6 mΩ BSZ086P03NS3E G R _{DS(on)} =8.6 mΩ		IRF9321 R _{DS(on)} =7.2 mΩ BSO080P03NS3 G R _{DS(on)} =8.0 mΩ		
					BSC084P03NS3 G R _{DS(on)} =8.4 mΩ BSC084P03NS3E G R _{DS(on)} =8.4 mΩ; ESD	BSO080P03NS3E G R _{DS(on)} =8.0 mΩ; ESD BSO080P03S H R _{DS(on)} =8.0 mΩ		
				BSZ120P03NS3 G R _{DS(on)} =12.0 mΩ BSZ120P03NS3E G R _{DS(on)} =12.0 mΩ; ESD		BSO301SP H R _{DS(on)} =8.0 mΩ IRF9328 R _{DS(on)} =11.9 mΩ IRF9388TRPBF R _{DS(on)} =11.9 mΩ		
					IRFHM9331 ²⁾ R _{DS(on)} =15 mΩ	BSO130P03S H R _{DS(on)} =13.0 mΩ IRF9358 R _{DS(on)} =16 mΩ; 双		
						IRF9332 R _{DS(on)} =17.5 mΩ IRF9392TRPBF R _{DS(on)} =17.5 mΩ		
				BSZ180P03NS3 G R _{DS(on)} =18.0 mΩ BSZ180P03NS3E G R _{DS(on)} =18.0 mΩ; ESD		IRF9333 R _{DS(on)} =19.4 mΩ BSO200P03S H R _{DS(on)} =20.0 mΩ		
						BSO303SP H R _{DS(on)} =21.0 mΩ BSO303P H R _{DS(on)} =21.0 mΩ; 双	IRFH9301TRPBF R _{DS(on)} =37.0 mΩ	
				IRLML9301TRPBF R _{DS(on)} =64 mΩ		IRF9362 R _{DS(on)} =21 mΩ; 双	IRFHS9351TRPBF R _{DS(on)} =170.0 mΩ; 双	IRFTS9342*** R _{DS(on)} =32 mΩ
				IRLML9303TRPBF R _{DS(on)} =165 mΩ		IRF9335 R _{DS(on)} =59 mΩ		



功率 P-沟道MOSFET



电压 [V]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-220	PQFN 3.3 x 3.3	SuperSO8	SO-8
-60	IPD380P06NM R _{DS(on)} = 38 mΩ	IPB110P06LM R _{DS(on)} = 11 mΩ	SPP80P06P H* R _{DS(on)} = 23.0 mΩ			
	IPD650P06NM R _{DS(on)} = 65 mΩ	SPB80P06P G* R _{DS(on)} = 23.0 mΩ				
	SPD30P06P G* R _{DS(on)} = 75.0 mΩ					
	IPD900P06NM R _{DS(on)} = 90 mΩ					
	SPD18P06P G* R _{DS(on)} = 130.0 mΩ	SPB18P06P G* R _{DS(on)} = 130.0 mΩ	SPP18P06P H* R _{DS(on)} = 130.0 mΩ			BSO613SPV G* R _{DS(on)} = 130.0 mΩ
	SPD09P06PL G* R _{DS(on)} = 250.0 mΩ					
	IPD25DP06LM R _{DS(on)} = 250 mΩ					
	IPD25DP06NM R _{DS(on)} = 250 mΩ					
	SPD08P06P G* R _{DS(on)} = 300.0 mΩ	SPB08P06P G* R _{DS(on)} = 300.0 mΩ	SPP08P06P H* R _{DS(on)} = 300.0 mΩ			
	IPD40DP06NM R _{DS(on)} = 400 mΩ					
	SPD15P10PL G* R _{DS(on)} = 200.0 mΩ		SPP15P10PL H* R _{DS(on)} = 200.0 mΩ			
	SPD15P10P G* R _{DS(on)} = 240.0 mΩ		SPP15P10P H* R _{DS(on)} = 240.0 mΩ			
-100	SPD04P10PL G* R _{DS(on)} = 850.0 mΩ					
	SPD04P10P G* R _{DS(on)} = 1000.0 mΩ					

互补功率MOSFET



电压 [V]	TO-252 (DPAK)	TO-263 (D ² PAK)	TO-220	PQFN 3.3 x 3.3	SuperSO8	SO-8
-20/20	>50 mΩ			BSZ15DC02KD H*** N: 55 mΩ, 5.1 A P: 150 mΩ, -3.2 A		
60年-60月	11-30 Ω			BSZ215C H*** N: 55 mΩ, 5.1 A P: 150 mΩ, -3.2 A		BSO612CV G* N: 0.12 Ω, 3.0 A P: 0.30 Ω, -2.0 A
						BSO615C G* N: 0.11 Ω, 3.1 A P: 0.30 Ω, -2.0 A

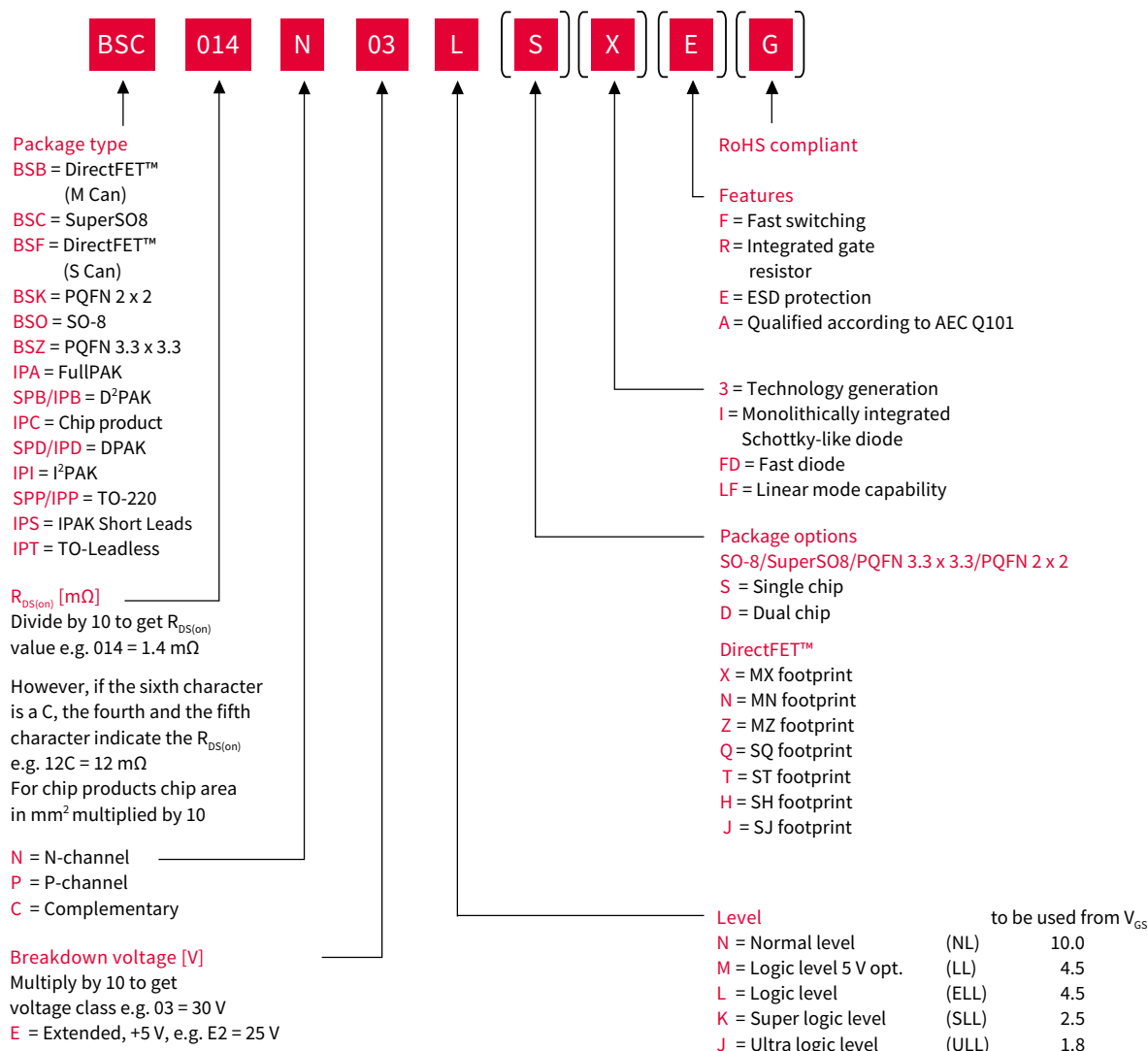
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*产品符合汽车AEC Q101

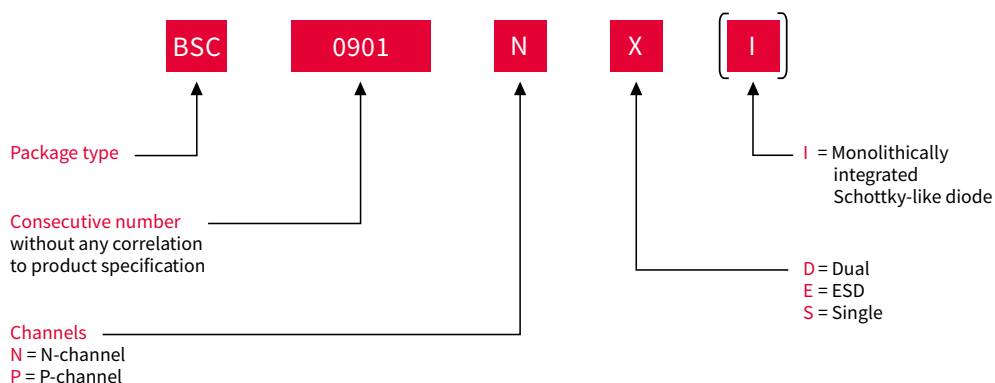
**R_{DS(on)} 于 4.5 V 规定

命名法

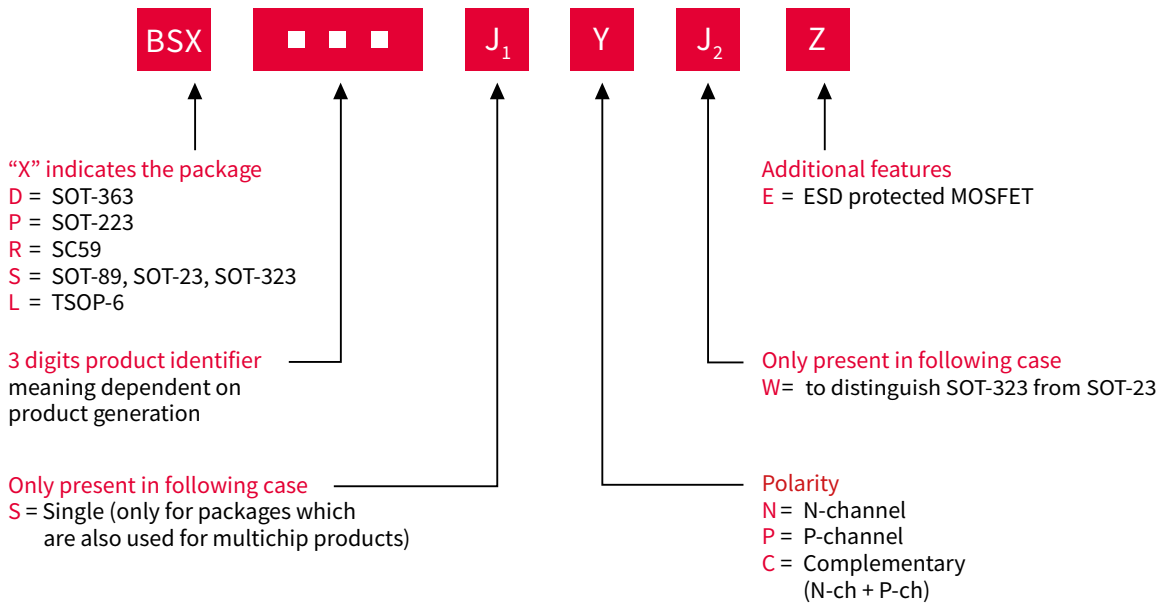
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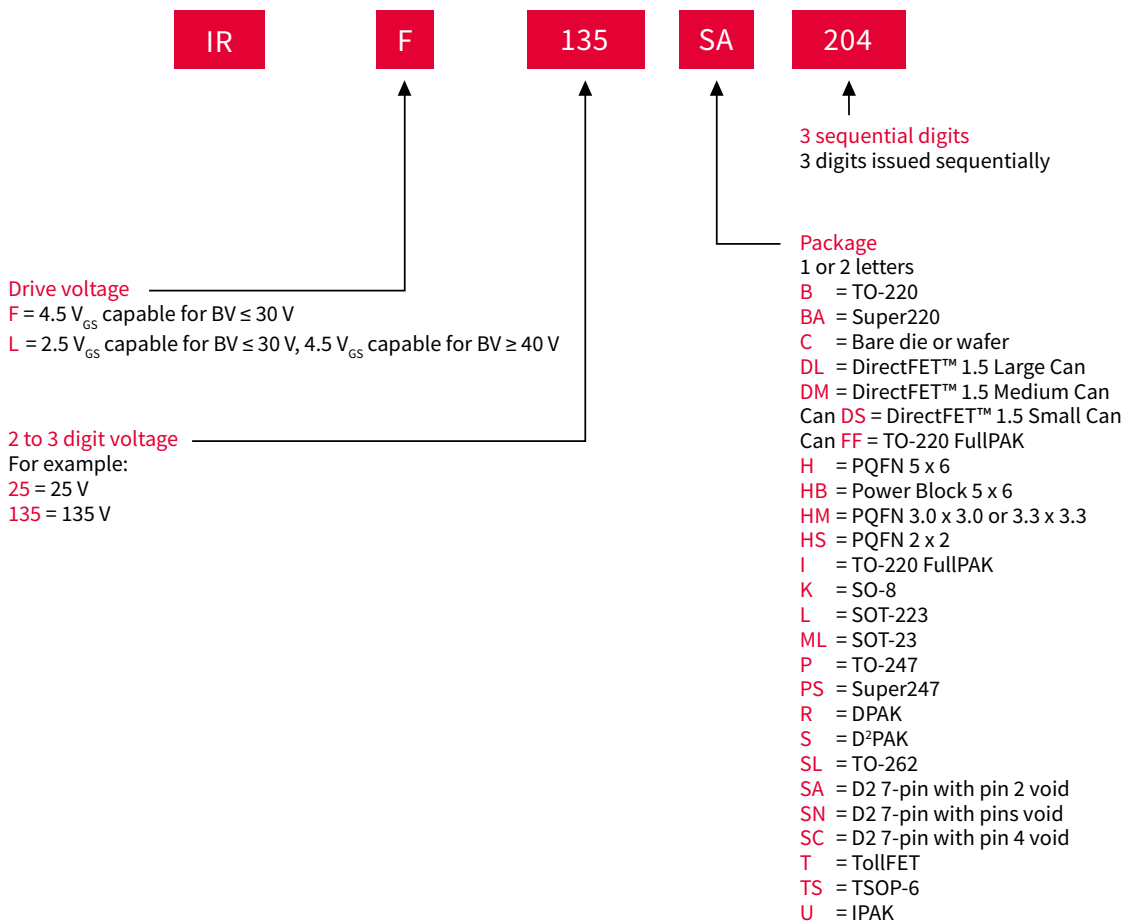
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Infineon Technologies Austria AG
9500 Villach, Austria

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Order number: B131-I0829-V1-5D00-AP-EC-P
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